Welcome to STN International! Enter x:x

LOGINID: SSSPTA1752YXC

PASSWORD:

TERMINAL (ENTER 1, 2, 3, OR ?):2

```
Welcome to STN International
                Web Page URLs for STN Seminar Schedule - N. America
NEWS
NEWS 2
                 "Ask CAS" for self-help around the clock
NEWS
        SEP 01 New pricing for the Save Answers for SciFinder Wizard within
                STN Express with Discover!
        OCT 28 KOREAPAT now available on STN
NEWS
     5 NOV 30 PHAR reloaded with additional data
NEWS
     6 DEC 01 LISA now available on STN
NEWS
        DEC 09
                12 databases to be removed from STN on December 31, 2004
NEWS
     7
        DEC 15
                MEDLINE update schedule for December 2004
NEWS
     9 DEC 17
                ELCOM reloaded; updating to resume; current-awareness
NEWS
                alerts (SDIs) affected
NEWS
     10 DEC 17
                COMPUAB reloaded; updating to resume; current-awareness
                 alerts (SDIs) affected
     11 DEC 17
NEWS
                SOLIDSTATE reloaded; updating to resume; current-awareness
                 alerts (SDIs) affected
                CERAB reloaded; updating to resume; current-awareness
NEWS
     12 DEC 17
                alerts (SDIs) affected
     13 DEC 17 THREE NEW FIELDS ADDED TO IFIPAT/IFIUDB/IFICDB
NEWS
NEWS 14 DEC 30 EPFULL: New patent full text database to be available on STN
NEWS 15 DEC 30 CAPLUS - PATENT COVERAGE EXPANDED
NEWS 16 JAN 03 No connect-hour charges in EPFULL during January and
                February 2005
NEWS 17 FEB 25 CA/CAPLUS - Russian Agency for Patents and Trademarks
                 (ROSPATENT) added to list of core patent offices covered
                STN Patent Forums to be held in March 2005
NEWS
     18 FEB 10
NEWS 19 FEB 16 STN User Update to be held in conjunction with the 229th ACS
                National Meeting on March 13, 2005
NEWS 20 FEB 28 PATDPAFULL - New display fields provide for legal status
                data from INPADOC
     21 FEB 28 BABS - Current-awareness alerts (SDIs) available
NEWS
     22 FEB 28 MEDLINE/LMEDLINE reloaded
NEWS
NEWS
     23 MAR 02 GBFULL: New full-text patent database on STN
NEWS
     24 MAR 03 REGISTRY/ZREGISTRY - Sequence annotations enhanced
NEWS 25 MAR 03 MEDLINE file segment of TOXCENTER reloaded
            JANUARY 10 CURRENT WINDOWS VERSION IS V7.01a, CURRENT
NEWS EXPRESS
              MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP),
              AND CURRENT DISCOVER FILE IS DATED 10 JANUARY 2005
              STN Operating Hours Plus Help Desk Availability
NEWS HOURS
NEWS INTER
              General Internet Information
NEWS LOGIN
             Welcome Banner and News Items
NEWS PHONE
             Direct Dial and Telecommunication Network Access to STN
             CAS World Wide Web Site (general information)
NEWS WWW
```

Enter NEWS followed by the item number or name to see news on that specific topic.

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FILE 'HOME' ENTERED AT 12:14:41 ON 07 MAR 2005

=> file reg

COST IN U.S. DOLLARS

SINCE FILE TOTAL ENTRY SESSION 0.21 0.21

FULL ESTIMATED COST

FILE 'REGISTRY' ENTERED AT 12:15:00 ON 07 MAR 2005 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2005 American Chemical Society (ACS)

Property values tagged with IC are from the ZIC/VINITI data file provided by InfoChem.

STRUCTURE FILE UPDATES: 4 MAR 2005 HIGHEST RN 842949-55-7 DICTIONARY FILE UPDATES: 4 MAR 2005 HIGHEST RN 842949-55-7

TSCA INFORMATION NOW CURRENT THROUGH JANUARY 18, 2005

Please note that search-term pricing does apply when conducting SmartSELECT searches.

Crossover limits have been increased. See HELP CROSSOVER for details.

Experimental and calculated property data are now available. For more information enter HELP PROP at an arrow prompt in the file or refer to the file summary sheet on the web at: http://www.cas.org/ONLINE/DBSS/registryss.html

=>Testing the current file.... screen

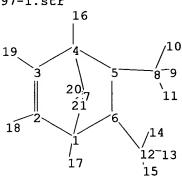
ENTER SCREEN EXPRESSION OR (END):end

=> screen 2067

L1 SCREEN CREATED

=>

Uploading C:\Program Files\Stnexp\Queries\10697397-1.str



chain nodes :

8 9 10 11 12 13 14 15 16 17 18 19 20 21

ring nodes :

1 2 3 4 5 6 7

chain bonds :

1-17 2-18 3-19 4-16 5-8 6-12 7-20 7-21 8-9 8-10 8-11 12-15 12-13 12-14

ring bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6

exact/norm bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 8-9 12-13 exact bonds : 1-17 2-18 3-19 4-16 5-8 6-12 7-20 7-21 8-10 8-11 12-15 12-14

Match level:

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS 16:CLASS 17:CLASS 18:CLASS 19:CLASS 20:CLASS 21:CLASS

L2STRUCTURE UPLOADED

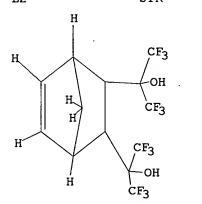
=> que L2 AND L1

QUE L2 AND L1 L3

=> d

L3 HAS NO ANSWERS

SCR 2067 L1L2 STR



Structure attributes must be viewed using STN Express query preparation. L3 QUE ABB=ON PLU=ON L2 AND L1

=> s 13 sss sam

SAMPLE SEARCH INITIATED 12:15:28 FILE 'REGISTRY' SAMPLE SCREEN SEARCH COMPLETED -3 TO ITERATE

100.0% PROCESSED

3 ITERATIONS

0 ANSWERS

SEARCH TIME: 00.00.01

FULL FILE PROJECTIONS: ONLINE **COMPLETE**

COMPLETE BATCH

PROJECTED ITERATIONS: 3 TO 163

PROJECTED ANSWERS: 0 TO

O SEA SSS SAM L2 AND L1 L4

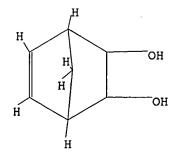
=>Testing the current file.... screen

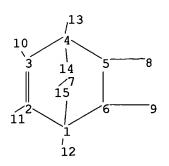
ENTER SCREEN EXPRESSION OR (END):end

=> screen 2067

L5 SCREEN CREATED

=> Uploading C:\Program Files\Stnexp\Queries\10697397-2.str





chain nodes :

8 9 10 11 12 13 14 15

ring nodes :

1 2 3 4 5 6 7

chain bonds :

1-12 2-11 3-10 4-13 5-8 6-9 7-14 7-15

ring bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6

exact/norm bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 5-8 6-9

exact bonds :

1-12 2-11 3-10 4-13 7-14 7-15

Match level:

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS

L6 STRUCTURE UPLOADED

=> que L6 AND L5

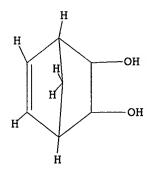
L7 QUE L6 AND L5

=> d

L7 HAS NO ANSWERS

L5 SCR 2067

L6 STR



Structure attributes must be viewed using STN Express query preparation. L7 QUE ABB=ON PLU=ON L6 AND L5

=> s 17 sss sam

SAMPLE SEARCH INITIATED 12:15:54 FILE 'REGISTRY'
SAMPLE SCREEN SEARCH COMPLETED - 148 TO ITERATE

100.0% PROCESSED 148 ITERATIONS

SEARCH TIME: 00.00.01

0 ANSWERS

FULL FILE PROJECTIONS: ONLINE **COMPLETE**

BATCH **COMPLETE**

PROJECTED ITERATIONS:

2231 TO 3689

PROJECTED ANSWERS:

0 TO

*1 OH

CF3

L8

O SEA SSS SAM L6 AND L5

=>Testing the current file.... screen

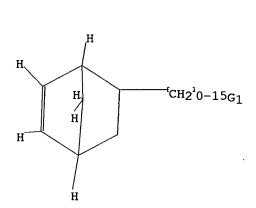
ENTER SCREEN EXPRESSION OR (END):end

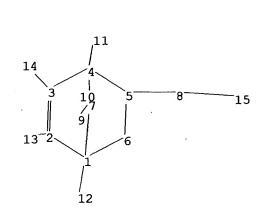
=> screen 2067

L9 SCREEN CREATED

=>

Uploading C:\Program Files\Stnexp\Queries\10697397-3.str





20 19122

21

chain nodes :

 $8 \quad 9 \quad 10 \quad 11 \quad 12 \quad 13 \quad 14 \quad 15 \quad 19 \quad 20 \quad 21 \quad 22$

ring nodes :

1 2 3 4 5 6 7

chain bonds :

1-12 2-13 3-14 4-11 5-8 7-9 7-10 8-15 19-20 19-21 19-22

ring bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6

exact/norm bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 8-15 19-22

exact bonds :

1-12 2-13 3-14 4-11 5-8 7-9 7-10 19-20 19-21

G1:H,F,CF3,OH,[*1]

Match level :

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS 19:CLASS 21:CLASS 22:CLASS

L10 STRUCTURE UPLOADED

=> que L10 AND L9

L11 QUE L10 AND L9

=> d

L11 HAS NO ANSWERS

L9 SCR 2067

L10

STR

$$\begin{array}{c} CF_{3} \\ CF_{3} \\ CF_{3} \\ H \end{array}$$

G1 H, F, CF3, OH, [@1]

Structure attributes must be viewed using STN Express query preparation. L11 QUE ABB=ON PLU=ON L10 AND L9

=> s 111 sss sam

SAMPLE SEARCH INITIATED 12:16:25 FILE 'REGISTRY' SAMPLE SCREEN SEARCH COMPLETED - 6622 TO ITERATE

15.1% PROCESSED

1000 ITERATIONS

INCOMPLETE SEARCH (SYSTEM LIMIT EXCEEDED)

SEARCH TIME: 00.00.01

FULL FILE PROJECTIONS:

ONLINE **COMPLETE**

BATCH **COMPLETE**

PROJECTED ITERATIONS:

127562 TO 137318

PROJECTED ANSWERS:

12824 TO 16046

CF3

CF3

*1 OH

L12

50 SEA SSS SAM L10 AND L9

=>Testing the current file.... screen

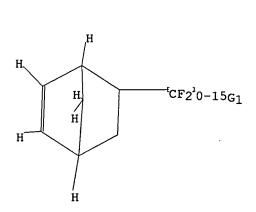
ENTER SCREEN EXPRESSION OR (END):end

=> screen 2067

L13 SCREEN CREATED

=>

Uploading C:\Program Files\Stnexp\Queries\10697397-4.str



50 ANSWERS

20 19122 21

chain nodes :

8 9 10 11 12 13 14 15 19 20 21 22
ring nodes:
1 2 3 4 5 6 7
chain bonds:
1-12 2-13 3-14 4-11 5-8 7-9 7-10 8-15 19-20 19-21 19-22
ring bonds:
1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6
exact/norm bonds:
1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 8-15 19-22
exact bonds:
1-12 2-13 3-14 4-11 5-8 7-9 7-10 19-20 19-21

G1:H,F,CF3,OH,[*1]

Match level:

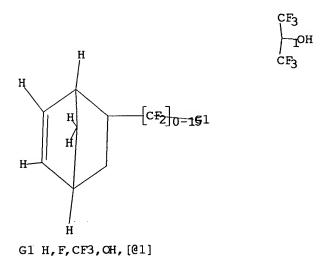
1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS 19:CLASS 20:CLASS 21:CLASS

L14 STRUCTURE UPLOADED

=> que L14 AND L13

L15 QUE L14 AND L13

=> d L15 HAS NO ANSWERS L13 SCR 2067 L14 STR



Structure attributes must be viewed using STN Express query preparation. L15 QUE ABB=ON PLU=ON L14 AND L13

=> s 115 sss sam SAMPLE SEARCH INITIATED 12:17:05 FILE 'REGISTRY' SAMPLE SCREEN SEARCH COMPLETED - 6622 TO ITERATE

15.1% PROCESSED 1000 ITERATIONS INCOMPLETE SEARCH (SYSTEM LIMIT EXCEEDED) SEARCH TIME: 00.00.01

FULL FILE PROJECTIONS: ONLINE **COMPLETE**
BATCH **COMPLETE**
PROJECTED ITERATIONS: 127562 TO 137318

50 ANSWERS

16046 12824 TO

L16

50 SEA SSS SAM L14 AND L13

=>Testing the current file.... screen

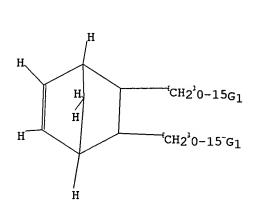
ENTER SCREEN EXPRESSION OR (END):end

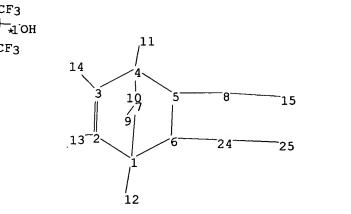
=> screen 2067

SCREEN CREATED L17

=>

Uploading C:\Program Files\Stnexp\Queries\10697397-5.str





20

21

19122

chain nodes : 8 9 10 11 12 13 14 15 19 20 21 22 24 25 ring nodes : 1 2 3 4 5 6 7 chain bonds : 1-12 2-13 3-14 4-11 5-8 6-24 7-9 7-10 8-15 19-20 19-21 19-22 24-25 ring bonds : 1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 exact/norm bonds : 1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 8-15 19-22 24-25 exact bonds : 1-12 2-13 3-14 4-11 5-8 6-24 7-9 7-10 19-20

CF3

G1:H,F,CF3,OH,[*1]

Match level:

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS 19:CLASS 20:CLASS 21:CLASS 22:CLASS 24:CLASS 25:CLASS

L18 STRUCTURE UPLOADED

=> que L18 AND L17

L19 QUE L18 AND L17

=> d

L19 HAS NO ANSWERS

L17 SCR 2067

L18 STR

H
$$H = \begin{bmatrix} CH_2 \\ 0-1 \end{bmatrix}$$

$$H = \begin{bmatrix} CH_2 \\ 0-1 \end{bmatrix}$$

$$H = \begin{bmatrix} CH_2 \\ 0-1 \end{bmatrix}$$

G1 H, F, CF3, OH, [@1]

Structure attributes must be viewed using STN Express query preparation. L19 QUE ABB=ON PLU=ON L18 AND L17

=> s 119 sss sam

STRUCTURE TOO LARGE - SEARCH ENDED

A structure in your query is too large. You may delete attributes or atoms to reduce the size of the structure and try again.

=> s 118 sss sam

STRUCTURE TOO LARGE - SEARCH ENDED

A structure in your query is too large. You may delete attributes or atoms to reduce the size of the structure and try again.

=>Testing the current file.... screen

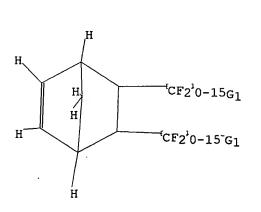
ENTER SCREEN EXPRESSION OR (END):end

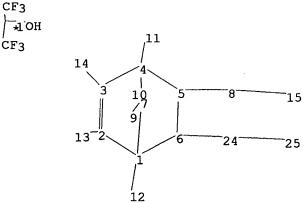
=> screen 2067

L20 SCREEN CREATED

=>

Uploading C:\Program Files\Stnexp\Queries\10697397-6.str





20

, 21

19122

chain nodes :
8 9 10 11 12 13 14 15 19 20 21 22 24 25
ring nodes :
1 2 3 4 5 6 7

chain bonds:
1-12 2-13 3-14 4-11 5-8 6-24 7-9 7-10 8-15 19-20 19-21 19-22 24-25 ring bonds:
1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 exact/norm bonds:
1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 8-15 19-22 24-25 exact bonds:
1-12 2-13 3-14 4-11 5-8 6-24 7-9 7-10 19-20 19-21

G1:H,F,CF3,OH,[*1]

Match level:

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS 19:CLASS 20:CLASS 21:CLASS 22:CLASS 24:CLASS 25:CLASS

L21 STRUCTURE UPLOADED

=> que L21 AND L20

L22 QUE L21 AND L20

=> d L22 HAS NO ANSWERS L20 SCR 2067 L21 STR

H
$$\begin{array}{c}
H \\
H \\
H
\end{array}$$

$$\begin{bmatrix}
CF_2 \\
0-1 \\
G_1
\end{bmatrix}$$

$$\begin{bmatrix}
CF_2 \\
0-1 \\
G_1
\end{bmatrix}$$

CF₃ OH CF₃

G1 H, F, CF3, OH, [@1]

Structure attributes must be viewed using STN Express query preparation. L22 QUE ABB=ON PLU=ON L21 AND L20

=> s 122 sss sam

STRUCTURE TOO LARGE - SEARCH ENDED

A structure in your query is too large. You may delete attributes or atoms to reduce the size of the structure and try again.

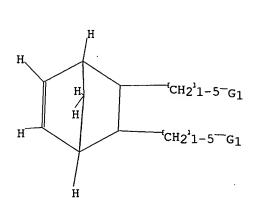
=>Testing the current file.... screen

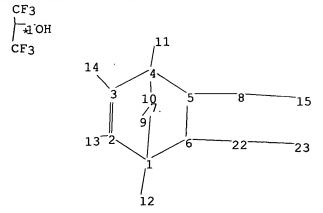
ENTER SCREEN EXPRESSION OR (END):end

=> screen 2067

=>

Uploading C:\Program Files\Stnexp\Queries\10697397-7.str





chain nodes :

8 9 10 11 12 13 14 15 17 18 19 20 22 23

ring nodes :

1 2 3 4 5 6 7

chain bonds :

1-12 2-13 3-14 4-11 5-8 6-22 7-9 7-10 8-15 17-18 17-19 17-20 22-23

ring bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6

exact/norm bonds :

1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 8-15 17-20 22-23

exact bonds :

1-12 2-13 3-14 4-11 5-8 6-22 7-9 7-10 17-18 17-19

G1:H,F,CF3,OH,[*1]

Match level:

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS 17:CLASS 18:CLASS 19:CLASS 20:CLASS 22:CLASS 23:CLASS

L24 STRUCTURE UPLOADED

=> que L24 AND L23

L25 QUE L24 AND L23

=> d

L25 HAS NO ANSWERS

L23 SCR 2067

L24 STR

18 17120 19

H
$$(CH_2)_{1-5}G1$$

$$(CH_2)_{1-5}G1$$

$$(CH_2)_{1-5}G1$$

G1 H, F, CF3, OH, [@1]

Structure attributes must be viewed using STN Express query preparation. QUE ABB=ON PLU=ON L24 AND L23 L25

=> s 125 sss sam

SAMPLE SEARCH INITIATED 12:20:42 FILE 'REGISTRY' SAMPLE SCREEN SEARCH COMPLETED -5344 TO ITERATE

18.7% PROCESSED

1000 ITERATIONS

INCOMPLETE SEARCH (SYSTEM LIMIT EXCEEDED)

SEARCH TIME: 00.00.01

FULL FILE PROJECTIONS:

ONLINE **COMPLETE**

COMPLETE BATCH

PROJECTED ITERATIONS:

102497 TO 111263

PROJECTED ANSWERS:

150 TO 704

CF3

CF3

L26

4 SEA SSS SAM L24 AND L23

=>Testing the current file.... screen

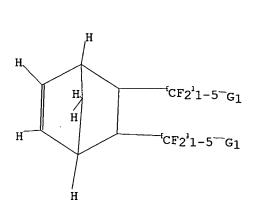
ENTER SCREEN EXPRESSION OR (END):end

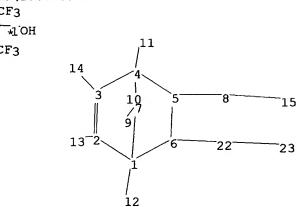
=> screen 2067

L27 SCREEN CREATED

=>

Uploading C:\Program Files\Stnexp\Queries\10697397-8.str





4 ANSWERS

18 17120 19

chain nodes :

8 9 10 11 12 13 14 15 17 18 19 20 22 23
ring nodes:
1 2 3 4 5 6 7
chain bonds:
1-12 2-13 3-14 4-11 5-8 6-22 7-9 7-10 8-15 17-18 17-19 17-20 22-23
ring bonds:
1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6
exact/norm bonds:
1-2 1-6 1-7 2-3 3-4 4-5 4-7 5-6 8-15 17-20 22-23
exact bonds:
1-12 2-13 3-14 4-11 5-8 6-22 7-9 7-10 17-18 17-19

G1:H, F, CF3, OH, [*1]

Match level :

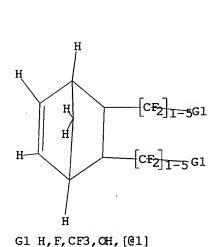
1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:CLASS 9:CLASS 10:CLASS 11:CLASS 12:CLASS 13:CLASS 14:CLASS 15:CLASS 17:CLASS 18:CLASS 19:CLASS 20:CLASS 22:CLASS 23:CLASS

L28 STRUCTURE UPLOADED

=> que L28 AND L27

L29 QUE L28 AND L27

=> d L29 HAS NO ANSWERS L27 SCR 2067 L28 STR



CF₃

CF₃

Structure attributes must be viewed using STN Express query preparation. L29 QUE ABB=ON PLU=ON L28 AND L27

=> s 129 sss sam SAMPLE SEARCH INITIATED 12:22:16 FILE 'REGISTRY' SAMPLE SCREEN SEARCH COMPLETED - 141 TO ITERATE

100.0% PROCESSED 141 ITERATIONS

0 ANSWERS

SEARCH TIME: 00.00.01

FULL FILE PROJECTIONS: ONLINE **COMPLETE**

BATCH **COMPLETE**

PROJECTED ITERATIONS: 2108 TO 3532

PROJECTED ANSWERS: 0 TO 0

L30 0 SEA SSS SAM L28 AND L27

=> FIL HCAPLUS, CAPLUS, USPATFULL

COST IN U.S. DOLLARS SINCE FILE TOTAL

FULL ESTIMATED COST ENTRY SESSION 5.16 5.37

FILE 'HCAPLUS' ENTERED AT 12:22:28 ON 07 MAR 2005
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FILE 'CAPLUS' ENTERED AT 12:22:28 ON 07 MAR 2005 USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT. PLEASE SEE "HELP USAGETERMS" FOR DETAILS. COPYRIGHT (C) 2005 AMERICAN CHEMICAL SOCIETY (ACS)

FILE 'USPATFULL' ENTERED AT 12:22:28 ON 07 MAR 2005
CA INDEXING COPYRIGHT (C) 2005 AMERICAN CHEMICAL SOCIETY (ACS)

=> s 14 or 18 or 112 or 116 or 126 or 130 L31 233 L4 OR L8 OR L12 OR L16 OR L26 OR L30

=> s photoresist or resist
L32 454502 PHOTORESIST OR RESIST

=> s 131 and 132

L33 148 L31 AND L32

=> duplicates remove 133
DUPLICATE PREFERENCE IS 'HCAPLUS, CAPLUS, USPATFULL'
KEEP DUPLICATES FROM MORE THAN ONE FILE? Y/(N):n
PROCESSING COMPLETED FOR L33

L34 86 DUPLICATE REMOVE L33 (62 DUPLICATES REMOVED)

=> d 134 1-86 ibib hitstr

L34 ANSWER 1 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 1

ACCESSION NUMBER: 2005:123212 HCAPLUS

DOCUMENT NUMBER: 142:198529

TITLE: Low polydispersity resin and preparation thereof using

chain-transfer agents

INVENTOR(S): Lee, Ting-Yu; Yu, Choa-Ying; Hsu, Meei-Yu; Wang,

Shian-Jy; Ting, Ching; Shih, Kuo-Chen

PATENT ASSIGNEE(S): Taiwan

SOURCE: U.S. Pat. Appl. Publ., 13 pp.

CODEN: USXXCO

DOCUMENT TYPE:

Patent English

LANGUAGE: FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

US 2005032997 A1 20050210 US 2003-714052 20031114

PRIORITY APPLN. INFO.: TW 2003-92121346 A 20030805

IT 254751-22-9P

RL: IMF (Industrial manufacture); PREP (Preparation)
(low polydispersity resin and preparation thereof using chain-transfer agents)

RN 254751-22-9 HCAPLUS

CN 2-Propenoic acid, methyl ester, polymer with 5-butylbicyclo[2.2.1]hept-2-ene (9CI) (CA INDEX NAME)

CRN 22094-81-1 CMF C11 H18

CM 2

CRN 96-33-3 CMF C4 H6 O2

0 MeO-C-CH CH2

L34 ANSWER 2 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 2

ACCESSION NUMBER:

2004:740363 HCAPLUS

DOCUMENT NUMBER: TITLE:

Vinyl addition polycyclic olefin polymers prepared

with non-olefinic chain transfer agents and their uses

in photoresist

141:261444

INVENTOR(S):

Rhodes, Larry F.; Barnes, Dennis A.; Bell, Andrew;

Bennett, Brian K.; Chang, Chung; Lipian, John-Henry;

Wu, Xiaoming

PATENT ASSIGNEE(S):

Promerus Llc, USA PCT Int. Appl., 87 pp.

SOURCE:

CODEN: PIXXD2

DOCUMENT TYPE:

Patent English

LANGUAGE: FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

	WO 2004076495			KIND DATE			APPLICATION NO.										
				A2		2004	0910	,							0040		
	WO 2004076495		A3 20041028														
	W:	ΑE,	ΑE,	AG,	AL,	AL,	AM,	AM,	AM,	AT,	ΑT,	ΑU,	ΑZ,	ΑZ,	BA,	BB,	BG,
		BG,	BR,	BR,	BW,	BY,	BY,	BZ,	BZ,	CA,	CH,	CN,	CN,	co,	co,	CR,	CR,
		CU,	CU,	CZ,	CZ,	DE,	DE,	DK,	DK,	DM,	DZ,	EC,	EC,	EE,	EE,	EG,	ES,
							GE,	-	-								
		•	•	•	•	•	KG,	•		•	•	•	•	-	-	-	
		•	•		-	•	LU,	•		-	-		-	-			
		,	MZ,	•	•	•		•	•	•	•	•	•	•	•		
	RW	: BW,				LS.	MW.	MZ.	SD.	SL.	SZ.	TZ.	UG,	ZM.	ZW,	AT,	BE,
							DK,										
		•	•	•	•	•	SI,	•	•			•					
							SN,	-	-	-	-		-		-		
							SN,			,	•	•	•	•	•	•	•
	US 200		•		•	•	•	•		US 2	004-	7825	47		2	0040	219
PRTO										US 2						0030	221
	PRIORITY APPLN. INFO.:								US 2								
OTHE	R SOURC	E(S):			MAR	РАТ	141:	2614						-	_		
IT	754231																
	734231		_				.	\ . n	nn /	D		\ .	m m *	/ m -		7	

IT

RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(vinyl addition polycyclic olefin polymers prepared with non-olefinic chain transfer agents and their uses in photoresist)

754231-22-6 HCAPLUS RN

CN Bicyclo[2.2.1]hept-5-ene-2-ethanol, α, α -bis(trifluoromethyl)-, polymer with 2-(bicyclo[2.2.1]hept-5-en-2-ylmethoxy)ethanol (9CI) INDEX NAME)

CM 1

CRN 754231-21-5 CMF C10 H16 O2

CM 2

CRN 196314-61-1 CMF C11 H12 F6 O

L34 ANSWER 3 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 3

ACCESSION NUMBER:

2004:252554 HCAPLUS

DOCUMENT NUMBER:

140:254085

TITLE:

Process for production of fluoropolymers for

resist

INVENTOR(S):

Araki, Takayuki; Ishikawa, Takuji; Koh, Meiten;

Toriumi, Minoru; Yamazaki, Tamio; Furukawa, Takamitsu;

Itani, Toshiro

PATENT ASSIGNEE(S):

Daikin Industries, Ltd., Japan; Semiconductor Leading

Edge Technologies, Inc.

SOURCE:

PCT Int. Appl., 70 pp. CODEN: PIXXD2

DOCUMENT TYPE:

Patent

1

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT	PATENT NO.			KIND DATE			APPLICATION NO.				DATE				
WO 2004	WO 2004024787			A1 20040325			WO 2003-JP11605				20030911				
W:	AE, A	G, AL,	AM,	AT,	AU,	ΑZ,	BA,	BB,	BG,	BR,	BY,	BZ,	CA,	CH,	CN,
	co, c	R, CU,	CZ,	DE,	DK,	DM,	DZ,	EC,	EE,	EG,	ES,	FI,	GB,	GD,	GE,
	GH, G	M, HR,	HU,	ID,	IL,	IN,	IS,	JP,	KE,	KG,	ΚP,	KR,	ΚZ,	LC,	LK,
	LR, L	S, LT,	LU,	LV,	MA,	MD,	MG,	MK,	MN,	MW,	MX,	MZ,	NI,	NO,	NZ,
	OM, P	G, PH,	PL,	PT,	RO,	RU,	SC,	SD,	SE,	SG,	SK,	SL,	SY,	ТJ,	TM,
	TN, T	R, TT,	TZ,	UA,	UG,	US,	UZ,	VC,	VN,	YU,	ZA,	ZM,	ZW		
RW:	GH, G	M, KE,	LS,	MW,	MZ,	SD,	SL,	SZ,	TZ,	ŪG,	ZM,	ZW,	AM,	ΑZ,	BY,
	KG, K	Z, MD,	RU,	TJ,	TM,	AT,	BE,	BG,	CH,	CY,	CZ,	DE,	DK,	EE,	ES,
	FI, F	R, GB,	GR,	HU,	ΙE,	IT,	LU,	MC,	NL,	PT,	RO,	SE,	SI,	SK,	TR,
	BF, B	J, CF,	CG,	CI,	CM,	GA,	GN,	GQ,	GW,	ML,	MR,	NE,	SN,	TD,	TG
PRIORITY APP	LN. IN	FO.:						JP 2	002-	2687	39	1	A 2	0020	913
								JP 2	003-	4445	5	1	A 2	0030	221 _

OTHER SOURCE(S):

MARPAT 140:254085

IT 669775-29-5P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(process for production of fluoropolymers for resist)

RN 669775-29-5 HCAPLUS

CN Bicyclo[2.2.1]hept-2-ene, 5-[1-(ethoxymethoxy)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl]-5,6,6-trifluoro-, polymer with tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 484649-18-5 CMF C13 H13 F9 O2

CM 2

CRN 116-14-3 CMF C2 F4

F F - C = C - F

REFERENCE COUNT: 4 THERE ARE 4 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 4 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 4

ACCESSION NUMBER:

2004:219904 HCAPLUS

DOCUMENT NUMBER:

140:278420

TITLE:

Chemical amplification type photoresist

composition

INVENTOR(S):

Kanna, Shinichi; Mizutani, Kazuyoshi; Sasaki, Tomoya

PATENT ASSIGNEE(S):

SOURCE:

Fuji Photo Film Co., Ltd., Japan U.S. Pat. Appl. Publ., 44 pp.

CODEN: USXXCO

DOCUMENT TYPE:

:

LANGUAGE:

Patent English

FAMILY ACC. NUM. COUNT:

r: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 2004053161	A1	20040318	US 2003-642182	20030818
US 6830871	B2	20041214		
JP 2004102264	A2	20040402	JP 2003-294268	20030818
PRIORITY APPLN. INFO.:			JP 2002-238122 A	20020819
IT 672937-74-5P				

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(chemical amplification type resist composition containing)

RN 672937-74-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-ethanol, α,α-bis(trifluoromethyl)-, polymer with 5-[2-[(cyclohexyloxy)methoxy]-3,3,3-trifluoro-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-ene and tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 672937-66-5 CMF C18 H24 F6 O2

CM 2

CRN 196314-61-1 CMF C11 H12 F6 O

CM 3

CRN 116-14-3 CMF C2 F4

L34 ANSWER 5 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 5

ACCESSION NUMBER:

2004:100629 HCAPLUS

DOCUMENT NUMBER:

140:154467

TITLE:

Photoresists, polymers and processes for

microlithography

INVENTOR(S):

Feiring, Andrew E.; Schadt, Frank L.

PATENT ASSIGNEE(S):

E. I. Du Pont De Nemours and Company, USA

SOURCE:

U.S. Pat. Appl. Publ., 23 pp., Cont.-in-part of U.S.

Ser. No. 806,096.

CODEN: USXXCO

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PAT	PATENT NO.			KIND DATE			APPLICATION NO.				DATE						
	US 2004023150						US 2002-108935			35	20020327			327			
	6849						2005			1							201
WO														19990921			
	W:	ΑE,	AL,	ΑU,	BA,	BB,	BG,	BR,	CA,	CN,	CR,	CU,	CZ,	EE,	GD,	GE,	HR,
		HU,	ID,	IL,	IN,	IS,	JP,	KP,	KR,	LC,	LK,	LR,	LT,	LV,	MG,	MK,	MN,
		MX,	NO,	NZ,	PL,	RO,	SG,	SI,	SK,	SL,	TR,	TT,	UA,	US,	UZ,	VN,	YU,
		ZA,	AM,	AZ,	BY,	KG,	ΚZ,	MD,	RU,	ТJ,	TM						
	RW:	GH,	GM,	KE,	LS,	MW,	SD,	SL,	SZ,	TZ,	ŪG,	ZW,	ΑT,	BE,	CH,	CY,	DE,
		DK,	ES,	FI,	FR,	GB,	GR,	ΙE,	IT,	LU,	MC,	NL,	PT,	SE,	BF,	ВJ,	CF,
		CG,	CI,	CM,	GA,	GN,	GW,	ML,	MR,	ΝE,	SN,	TD,	TG				
US	6593	058			В1		2003	0715		US 2	001-	3060	96		2	0010	323
PRIORITY	APP	LN.	INFO	.:					•	US 1	998-	1015	02P]	P 1	9980	923
									1	WO 1	999-1	JS21	912	I	A1 1	9990	921
										US 2	001-	3060	96	Ž	A2 2	0010	323
										US 2	001-	2802	68P	1	P 2	0010	330

IT 262617-09-4P

RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(polymers and processes for photoresists and microlithog.)

RN 262617-09-4 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, polymer with

bicyclo[2.2.1]hept-2-ene and tetrafluoroethene (9CI) (CA INDEX NAME)

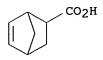
CM 1

CRN 498-66-8 CMF C7 H10



CM 2

CRN 120-74-1 CMF C8 H10 O2



CM 3

CRN 116-14-3 CMF C2 F4

L34 ANSWER 6 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 6

ACCESSION NUMBER:

2004:550129 HCAPLUS

DOCUMENT NUMBER:

SOURCE:

141:114064

TITLE:

Positive-working resist composition

containing base compound having one or more cyclic

ether group for improved line edge roughness

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 91 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

LANGUAGE:

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE	
JP 2004191649 PRIORITY APPIN. INFO.:	A 2	20040708	JP 2002-359631 JP 2002-359631	20021211	

IT 398141-14-5

RL: PRP (Properties); TEM (Technical or engineered material use); USES

(pos.-working resist composition containing base compound having one or more cyclic ether group for improved line edge roughness)

RN 398141-14-5 HCAPLUS

> Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CN

CRN 398140-58-4 CMF C13 H20 O2

CM2

CRN 342648-11-7 C13 H22 O2 CMF

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 7 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 7 ACCESSION NUMBER: 2004:389970 HCAPLUS

140:383121

DOCUMENT NUMBER:

TITLE: F2 excimer laser-sensitive positive

photoresist compositions with good coatability

and dry etchability

INVENTOR(S):

Kanna, Shinichi; Mizutani, Kazuyoshi; Sasaki, Tomoya

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 65 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2004138887 PRIORITY APPLN. INFO.:	A2	20040513	JP 2002-304421 JP 2002-304421	20021018 20021018

IT 685523-13-1

RL: TEM (Technical or engineered material use); USES (Uses) (F2 excimer laser-sensitive pos. photoresists with good coatability and dry etchability)

RN 685523-13-1 HCAPLUS

CN Carbonic acid, 1-(bicyclo[2.2.1]hept-5-en-2-ylmethyl)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl 1,1-dimethylethyl ester, polymer with 1-[(trifluoroethenyl)oxy]tricyclo[3.3.1.13,7]decane (9CI) (CA INDEX NAME)

CM 1

CRN 685522-91-2 CMF C12 H15 F3 O

CM 2

CRN 196314-63-3 CMF C16 H20 F6 O3

L34 ANSWER 8 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 8

ACCESSION NUMBER:

2004:307727 HCAPLUS

DOCUMENT NUMBER:

140:347500

TITLE:

Positive-working resists suppressing

development defects and forming precision square

profiles

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 69 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

LANGUAGE:

SOURCE:

Patent Japanese

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2004117677	A2	20040415	JP 2002-279190	20020925
PRIORITY APPLN. INFO.:			JP 2002-279190	20020925

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses)
(chemical amplified pos. resists containing carbonyloxycarbonylcontaining long-chain hydrocarbons and suppressing development defects)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 9 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 9

ACCESSION NUMBER:

2004:118481 HCAPLUS

DOCUMENT NUMBER:

140:189982

TITLE:

Positive **photoresist** composition with good post exposure delay stability and **resist**

profile

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S): SOURCE:

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 76 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2004045856 PRIORITY APPLN. INFO.:	A2	20040212	JP 2002-204340 JP 2002-204340	20020712 20020712

IT 398141-14-5P

RL: IMF (Industrial manufacture); POF (Polymer in formulation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (pos. photoresist composition with good post exposure delay stability and resist profile)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6

CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 10 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 10

ACCESSION NUMBER: 2004:753223 HCAPLUS

DOCUMENT NUMBER: 141:268557

TITLE: Positive resist composition and method of

forming a **resist** pattern using the same

APPLICATION NO.

DATE

INVENTOR(S): Sasaki, Tomoya

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

KIND

SOURCE: Eur. Pat. Appl., 80 pp.

CODEN: EPXXDW

DATE

DOCUMENT TYPE: Patent LANGUAGE: English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.

EP 1457819	A2	20040915	EP 2004-4961	20040303			
EP 1457819	A3	20041020					
R: AT, BE, CH,	DE, D	OK, ES, FR,	GB, GR, IT, LI, LU,	NL, SE, MC, PT,			
IE, SI, LT,	LV, F	FI, RO, MK,	CY, AL, TR, BG, CZ,	EE, HU, PL, SK			
JP 2004279471	A2	20041007	JP 2003-67010	20030312			
PRIORITY APPLN. INFO.:			JP 2003-67010	A 20030312			
IT 756532-47-5P							
DI . DDD /Droperties	1 . SDN	I (Synthetic	nreparation) TEM /	Technical or			

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. photoresist composition for forming resist pattern)

RN 756532-47-5 HCAPLUS

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 2-(trifluoromethyl)-, 3,5-dihydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with 1-ethenyl-3,5-bis[1-(ethoxymethoxy)-2,2,2-trifluoro-1-(trifluoromethyl)ethyl]benzene and 2,2,2-trifluoro-1-[4-[2,2,2-trifluoro-1-hydroxy-1-(trifluoromethyl)ethyl]phenyl]-1-(trifluoromethyl)ethyl 2-(trifluoromethyl)-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CN

CRN 756532-46-4 CMF C16 H7 F15 O3

CM 2

CRN 731861-90-8 CMF C19 H23 F3 O4

CM 3

CRN 585573-40-6 CMF C20 H20 F12 O4

$$\begin{array}{c|c} \text{CF3} & \text{CF3} \\ & & \\ & & \\ \text{F3C-C} & \\ \text{EtO-CH}_2\text{-O} & \text{O-CH}_2\text{-OEt} \\ \\ & & \\ \text{H}_2\text{C--CH} \end{array}$$

L34 ANSWER 11 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2004:292075 USPATFULL

TITLE:

Vinyl addition polycyclic olefin polymers prepared with .

non-olefinic chain transfer agents and uses thereof

INVENTOR(S):

Rhodes, Larry F., Silver Lake, OH, UNITED STATES
Barnes, Dennis A., Medina, OH, UNITED STATES

Bell, Andrew, Lakewood, OH, UNITED STATES

Bennet, Brian K., Brecksville, OH, UNITED STATES

Chang, Chun, Stow, OH, UNITED STATES

Lipian, John-Henry, Medina, OH, UNITED STATES Wu, Xiaoming, Strongsville, OH, UNITED STATES

PATENT ASSIGNEE(S):

Promerus LLC (U.S. corporation)

APPLICATION INFO.:

US 2004-782547 A1 20040219 (10)

NUMBER DATE

PRIORITY INFORMATION:

US 2003-448939P 20030221 (60)

DOCUMENT TYPE: FILE SEGMENT:

Utility APPLICATION

LEGAL REPRESENTATIVE: Paul M. Reznick, WEBB ZIESENHEIM LOGSDON, ORKIN &

HANSON, P.C., 436 Seventh Avenue, 700 Koppers Building,

Pittsburgh, PA, 15219-1818

NUMBER OF CLAIMS: EXEMPLARY CLAIM:

75 1

NUMBER OF DRAWINGS:

8 Drawing Page(s)

LINE COUNT:

2722

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

754231-22-6P

(vinyl addition polycyclic olefin polymers prepared with non-olefinic chain transfer agents and their uses in photoresist)

754231-22-6 USPATFULL RN

Bicyclo[2.2.1]hept-5-ene-2-ethanol, α, α -bis(trifluoromethyl)-, CN

polymer with 2-(bicyclo[2.2.1]hept-5-en-2-ylmethoxy)ethanol (9CI) (CA

INDEX NAME)

1 CM

CRN 754231-21-5 CMF C10 H16 O2

CM 2

CRN 196314-61-1 CMF C11 H12 F6 O

L34 ANSWER 12 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2004:178197 USPATFULL

TITLE:

Photosensitive polymer including copolymer of alkyl

vinyl ether and resist composition containing

the same

INVENTOR(S):

Choi, Sang-Jun, Seoul, KOREA, REPUBLIC OF

....

Kim, Hyun-Woo, Seongnam-city, KOREA, REPUBLIC OF

	NUMBER	KIND	DATE
PATENT INFORMATION:	US 2004137363	A1	20040715
APPLICATION INFO.:	us 2003-704977	A1	20031112 (10)
RELATED APPLN. INFO.:	Division of Ser.	No. US	2001-764150, f:

....

iled on 19 Jan 2001, GRANTED, Pat. No. US 6673513 Continuation-in-part

of Ser. No. US 2000-576053, filed on 23 May 2000,

GRANTED, Pat. No. US 6517990

	NUMBER	DATE
PRIORITY INFORMATION:	KR 2000-2489	20000119
	KR 2000-20603	20000419
	US 2000-198761P	20000421 (60)
DOCUMENT TYPE:	Utility	

FILE SEGMENT:

APPLICATION

LEGAL REPRESENTATIVE: JONES VOLENTINE, L.L.C., Suite 150, 12200 Sunrise

Valley Drive, Reston, VA, 20191

NUMBER OF CLAIMS:

EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 2 Drawing Page(s)

48

LINE COUNT: 1116

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 350992-45-9P

(chemical amplified photoresists containing alkyl vinyl ether polymers for ArF

excimer laser exposure)

RN 350992-45-9 USPATFULL

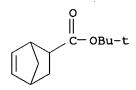
CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester,

polymer with 3,4-dihydro-2H-pyran and 2,5-furandione (9CI) (CA INDEX

NAME)

CM 1

CRN 154970-45-3 CMF C12 H18 O2



CM 2

CRN 110-87-2 CMF C5 H8 O



CM 3

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 13 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2004:31015 USPATFULL

TITLE:

Photoresists, polymers and processes for

TETATO

microlithography

\#D/DDD

INVENTOR(S):

Feiring, Andrew Edward, Wilmington, DE, UNITED STATES

D 3 m D

Feldman, Jerald, Hockessin, DE, UNITED STATES

	NUMBER	KIND	DATE		
		-			
PATENT INFORMATION:	US 2004023152	A1	20040205		
APPLICATION INFO.:	US 2003-437760	A1	20030514	(10)	
RELATED APPLN. INFO.:	Continuation of	Ser. No.	. US 2001-	806096.	fi

RELATED APPLN. INFO.: Continuation of Ser. No. US 2001-806096, filed of Mar 2001, GRANTED, Pat. No. US 6593058 A 371 of

International Ser. No. WO 1999-US21912, filed on 21 Sep

1999, PENDING

NUMBER DATE

PRIORITY INFORMATION: US 1998-101502P 19980923 (60) US 1999-120045P 19990212 (60)

US 1999-120045P Utility

FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: E I DU PONT DE NEMOURS AND COMPANY, LEGAL PATENT RECORDS CENTER, BARLEY MILL PLAZA 25/1128, 4417

LANCASTER PIKE, WILMINGTON, DE, 19805

NUMBER OF CLAIMS: 26 EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 1 Drawing Page(s)

LINE COUNT: 1800

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 262617-09-4P, Norbornene-5-norbornene-2-carboxylic

acid-tetrafluoroethylene copolymer

(preparation and use in preparing UV photoresists for microlithog.)

RN 262617-09-4 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, polymer with

bicyclo[2.2.1]hept-2-ene and tetrafluoroethene (9CI) (CA INDEX NAME)

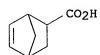
CM 1

CRN 498-66-8 CMF C7 H10



CM 2

CRN 120-74-1 CMF C8 H10 O2



CM 3

CRN 116-14-3 CMF C2 F4

L34 ANSWER 14 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2004:7949 USPATFULL

TITLE: Polymeric compound and resin composition for

photoresist

INVENTOR(S): Funaki, Yoshinori, Himeji-shi, JAPAN

Tsutsumi, Kiyoharu, Himeji-shi, JAPAN Takaragi, Akira, Himeji-shi, JAPAN

PATENT ASSIGNEE(S): Daicel Chemical Industries, Ltd. (non-U.S. corporation)

NUMBER KIND DATE

PATENT INFORMATION: US 2004006189 A1 20040108 US 6806335 B2 20041019

APPLICATION INFO.: US 2003-375129 A1 20030228 (10)

RELATED APPLN. INFO.: Continuation of Ser. No. US 2001-937910, filed on 19

Oct 2001, GRANTED, Pat. No. US 6552143 A 371 of International Ser. No. WO 2001-JP515, filed on 26 Jan

2001, UNKNOWN

NUMBER DATE

PRIORITY INFORMATION: JP 2000-24527 20000201

DOCUMENT TYPE: Utility
FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: BIRCH STEWART KOLASCH & BIRCH, PO BOX 747, FALLS

CHURCH, VA, 22040-0747

NUMBER OF CLAIMS: 6
EXEMPLARY CLAIM: 1
LINE COUNT: 3064

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 353289-59-5P

(polymeric compound for photoresist and resin composition for photoresist)

RN 353289-59-5 USPATFULL

CN Tricyclo[3.3.1.13,7]decane-1-carboxylic acid, 3-[(1-oxo-2-propenyl)oxy]-,

1,1-dimethylethyl ester, polymer with 2,5-furandione, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate and

3a,4,7,7a-tetrahydro-4,7-methanoisobenzofuran-1(3H)-one (9CI) (CA INDEX

NAME)

CM 1

CRN 251563-20-9 CMF C18 H26 O4

CM 2

CRN 216581-76-9 CMF C13 H18 O3

CRN 85718-44-1 CMF C9 H10 O2

CM 4

CRN 108-31-6 CMF C4 H2 O3

0000

L34 ANSWER 15 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2004:205768 USPATFULL

TITLE:

Copolymers and photoresist compositions

comprising same

INVENTOR(S):

Barclay, George G., Jefferson, MA, United States Caporale, Stefan J., Worcester, MA, United States

Yueh, Wang, Shrewsbury, MA, United States Mao, Zhibiao, Shrewsbury, MA, United States Mattia, Joseph, Framingham, MA, United States

PATENT ASSIGNEE(S):

Shipley Company, L.L.C., Marlborough, MA, United States

(U.S. corporation)

NUMBER	KIND	DATE

PATENT INFORMATION: APPLICATION INFO.:

US 6777157 B1 20040817 US 2000-567814 20000509 (9)

NUMBER DATE

PRIORITY INFORMATION:

US 2000-185345P 20000226 (60)

DOCUMENT TYPE: FILE SEGMENT:

Utility

PRIMARY EXAMINER:

GRANTED Ashton, Rosemary

LEGAL REPRESENTATIVE:

Corless, Peter F., Frickey, Darryl P., Edwards &

Angell, LLP

NUMBER OF CLAIMS:

15

EXEMPLARY CLAIM:

1

NUMBER OF DRAWINGS:

0 Drawing Figure(s); 0 Drawing Page(s)

LINE COUNT:

929

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 355395-09-4P

(photoresist composition containing photoacid labile acrylate and cyclic olefin)

RN 355395-09-4 USPATFULL

CN 2-Propenoic acid, 2-methyl-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester,

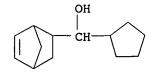
polymer with bicyclo[2.2.1]hept-2-ene, α -

cyclopentylbicyclo[2.2.1]hept-2-ene-2-methanol and 2,5-furandione (9CI)

(CA INDEX NAME)

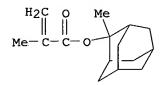
CM 1

CRN 355395-08-3 CMF C13 H20 O



CM 2

CRN 177080-67-0 CMF C15 H22 O2



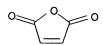
CM 3

CRN 498-66-8 CMF C7 H10



CM 4

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 16 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 11

ACCESSION NUMBER:

2003:42890 HCAPLUS

DOCUMENT NUMBER: TITLE:

138:115058

TITLE:

Resist composition and patterning process

INVENTOR(S): Kobayashi, Tomohiro; Nishi, Tsunehiro; Watanabe,

Satoshi; Kinsho, Takeshi; Nagura, Shigehiro; Ishihara,

Toshinobu

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Co., Ltd., USA

U.S. Pat. Appl. Publ., 35 pp.

CODEN: USXXCO

DOCUMENT TYPE:

Patent

LANGUAGE:

SOURCE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 2003013039	A1	20030116	US 2002-170345	20020614

US 6830866 B2 20041214 JP 2003066612 JP 2002-168143 20020610 A2 20030305 TW 2002-91113198 20030821 20020614 TW 548518 В A 20010615 JP 2001-181079 PRIORITY APPLN. INFO.:

IT 485818-88-0P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(photoresist composition and patterning process containing)

RN 485818-88-0 HCAPLUS

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-octahydro-, 1-ethylcyclopentyl ester, polymer with 1,3,3a,4,7,7a-hexahydro-4,7-epoxyisobenzofuran (9CI) (CA INDEX NAME)

CM 1

CRN 479075-40-6 CMF C8 H10 O2

CM 2

CRN 279243-82-2 CMF C20 H28 O2

L34 ANSWER 17 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 12

ACCESSION NUMBER: 2003:907516 HCAPLUS

DOCUMENT NUMBER: 139:388490

TITLE: Chemically amplified positive resists

producing defect-free patterns with square profile

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S): SOURCE:

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 60 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

LANGUAGE:

Japain

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
JP 2003330195	A2	20031119	JP 2002-279433		20020925
PRIORITY APPLN. INFO.:			JP 2002-60445	A	20020306
OTHER SOURCE(S):	MARPAT	139:388490			

IT 398141-14-5P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(chemical amplified pos. photoresists containing Meldrum's acid derivs. and producing patterns with square profile)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CRN 398140-58-4 CMF C13 H20 O2

CM2

342648-11-7 CRN CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 18 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 13

ACCESSION NUMBER:

2003:735196 HCAPLUS

DOCUMENT NUMBER:

139:267983

TITLE:

Positive-working **photoresist** composition

containing polymer with fluoro-aliphatic group

INVENTOR(S): Fujimori, Toru

PATENT ASSIGNEE(S): SOURCE:

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 88 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003262952	A2	20030919	JP 2002-65444	20020311
PRIORITY APPLN. INFO.:			JP 2002-65444	20020311

IT 398141-14-5P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. **photoresist** composition containing polymer with fluoro-aliphatic group)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 19 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 14

ACCESSION NUMBER:

2003:432993 HCAPLUS

DOCUMENT NUMBER:

139:28625

TITLE:

Positive photoresist compositions with

suppressed edge roughness

INVENTOR(S): PATENT ASSIGNEE(S): SOURCE:

Fujimori, Toru; Kawamura, Koichi Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 89 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO. DA	TE
JP 2003162061	A2	20030606	JP 2002-219789 20	020729
PRIORITY APPLN. INFO.:			JP 2001-279708 A 20	010914
OTHER SOURCE(S):	MARPAT	139:28625		

IT 398141-14-5P

> RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. photoresists containing sulfonimides with suppressed edge roughness)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

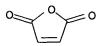
CRN 398140-58-4 CMF C13 H20 O2

CM

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3



CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 20 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 15

ACCESSION NUMBER:

2003:412090 HCAPLUS

DOCUMENT NUMBER:

139:14956

TITLE:

Far-UV-sensitive positive photoresists

forming fine patterns through half-tone phase-shift

masks

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 91 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003156848 PRIORITY APPLN. INFO.:	A2	20030530	JP 2001-357766 JP 2001-357766	20011122 20011122

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses)

(far-UV amplified pos. **photoresists** containing F-containing N compds. and suppressing side lobe phenomena in lithog. using half-tone masks)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 21 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 16

ACCESSION NUMBER: 2003:412089 HCAPLUS

DOCUMENT NUMBER: 139:14955

TITLE: Chemically amplified far-UV-sensitive positive

resists producing defect-free patterns

INVENTOR(S): Fujimori, Toru

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 93 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003156845 PRIORITY APPLN. INFO.:	A2 .	20030530	JP 2001-353163 JP 2001-353163	20011119 20011119

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses) (chemical amplified far-UV pos. resists containing polymers having alicyclic groups in main and/or side chains and sp. F compds.)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 22 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 17

ACCESSION NUMBER:

2003:317556 HCAPLUS

DOCUMENT NUMBER:

138:346480

TITLE:

SOURCE:

Positive chemically amplified resist

compositions having improved edge roughness of

patterns and high sensitivity

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 96 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

1

LANGUAGE: FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003122010	A2	20030425	JP 2001-318242	20011016
PRIORITY APPLN. INFO.:			JP 2001-318242	20011016

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses) (pos. chemical amplified resist compns. containing cycloolefin polymers and having improved edge roughness of patterns and high sensitivity)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 23 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 18

ACCESSION NUMBER: 2003:754897 HCAPLUS

DOCUMENT NUMBER: 139:252537

TITLE: Positive resist composition

INVENTOR(S): Fujimori, Toru

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Eur. Pat. Appl., 89 pp.

CODEN: EPXXDW

DOCUMENT TYPE: Patent LANGUAGE: English

FAMILY ACC. NUM. COUNT: 2 PATENT INFORMATION:

PATI	ent n	0.			KINI	D 1	DATE		7	APP	LICAT	'ION	NO.		D.	ATE	
									-						_		
EP 3	13473	35			A1	:	2003	0924	F	EΡ	2003-	6122			2	00303	318
	R:	ΑT,	BE,	CH,	DE,	DK,	ES,	FR,	GB,	GR	, IT,	LI,	LU,	NL,	SE,	MC,	PT,
		IE,	SI,				RO,	MK,	CY,	AL	, TR,	BG,	CZ,	EE,	HU,	SK	
JP 2	20032	7079	1		A2	:	2003	0925	j	JP	2002-	7456	5		2	0020	318
US 2	20032	2428	37		A 1	:	2003	1204	τ	JS	2003-	3884	80		2	00303	317
PRIORITY	APPL	N. I	NFO	. :					Ċ	JΡ	2002-	7456	5		A 2	00203	318

IT 398141-14-5P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. photoresist composition containing)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CRN 108-31-6 CMF C4 H2 O3

CM

CRN 79-10-7 C3 H4 O2 CMF

3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS REFERENCE COUNT: RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 24 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 19

ACCESSION NUMBER:

2003:241052 HCAPLUS

DOCUMENT NUMBER:

138:262693

TITLE:

Positive photoresist composition Fujimori, Toru; Kawabe, Yasumasa Fuji Photo Film Co., Ltd., Japan

PATENT ASSIGNEE(S):

Eur. Pat. Appl., 101 pp.

SOURCE:

INVENTOR(S):

CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1296190	A1	20030326	EP 2002-21204	20020918
R: AT, BE, CH,	DE, DK	, ES, FR,	GB, GR, IT, LI, LU, NL,	SE, MC, PT,
IE, SI, LT,	LV, FI	, RO, MK,	CY, AL, TR, BG, CZ, EE,	SK
JP 2003167333	A2	20030613	JP 2002-563	20020107
US 2003134225	A1	20030717	US 2002-244070	20020916
PRIORITY APPLN. INFO.:			JP 2001-285180	A 20010919
			JP 2002-563	A 20020107

IT

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. photoresist composition containing)

398141-14-5 HCAPLUS RN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, CN polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CRN 342648-11-7 CMF C13 H22 O2

CM

CRN 108-31-6 CMF C4 H2 O3

CM

CRN 79-10-7 CMF C3 H4 O2

REFERENCE COUNT:

THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 25 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 20

ACCESSION NUMBER:

2003:20986 HCAPLUS

DOCUMENT NUMBER:

138:98194

5

TITLE:

Positive photosensitive composition

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

SOURCE:

Eur. Pat. Appl., 135 pp.

CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

APPLICATION NO. DATE PATENT NO. KIND DATE

EP	1273	970			A2	200	3010	3	EP 2	002-	1488	9		2	0020	705
EP	1273	970			А3	200	04012	3								
	R:	AT,	BE,	CH,	DE,	DK, ES	s, FR	GB,	GR,	IT,	LI,	LU,	NL,	SE,	MC,	PT,
		IE,	SI,	LT,	LV,	FI, RO	O, MK	CY,	AL,	TR,	BG,	CZ,	EE,	SK		
JP	2003	02190	05		A2	200	3012	i	JP 2	001-	2066	37		2	0010	706
JP	2003	0986	72		A2	200	03040	1	JP 2	001-	2871	12		2	0010	920
US	2003	1861	61		A1	200	031002	2	US 2	002-	1882	24	•	2	0020	703
JP	2003	08444	41		A2	200	3031	•	JP 2	002-	1961	13		2	0020	704
TW	5860	52			В	200	04050	L	TW 2	002-	9111	4923		2	0020	705
PRIORITY	APP	LN.	INFO	. :					JP 2	001-	2049	69		A 2	0010	705
									JP 2	001-	2066	37		A 2	0010	706
									TP 2	001-	2871	12		A 2	0010	920

IT 398141-14-5P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. photosensitive composition containing)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7

L34 ANSWER 26 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2003:318544 USPATFULL

TITLE: Positive resist composition INVENTOR(S): Fujimori, Toru, Shizuoka, JAPAN

PATENT ASSIGNEE(S): FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)

APPLICATION INFO.: US 2003-388408 A1 20030317 (10)

NUMBER DATE

PRIORITY INFORMATION: JP 2002-74565 20020318

DOCUMENT TYPE: Utility
FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W.,

WASHINGTON, DC, 20037

NUMBER OF CLAIMS: 8
EXEMPLARY CLAIM: 1
LINE COUNT: 2427

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 398141-14-5P

(pos. photoresist composition containing)

RN 398141-14-5 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl

2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

108-31-6 CRN CMF C4 H2 O3



CM

79-10-7 CRN CMF C3 H4 O2

L34 ANSWER 27 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2003:306309 USPATFULL

TITLE:

Novel copolymers and photoresist compositions

comprising same

INVENTOR(S):

Barclay, George G., Jefferson, MA, UNITED STATES Caporale, Stefan J., Worcester, MA, UNITED STATES

Yueh, Wang, Shrewsbury, MA, UNITED STATES Mao, Zhibiao, Shrewsbury, MA, UNITED STATES Mattia, Joseph, Framingham, MA, UNITED STATES

NUMBER	KIND	DATE
US 2003215742	A1	20031120

PATENT INFORMATION:

US 6849381 B2 20050201

APPLICATION INFO .:

US 2003-408522 A1 20030407 (10)

RELATED APPLN. INFO.:

Continuation of Ser. No. US 2000-567814, filed on 9 May

2000, PENDING

DATE NUMBER

PRIORITY INFORMATION:

US 2000-185345P 20000226 (60)

DOCUMENT TYPE:

Utility

FILE SEGMENT:

APPLICATION

LEGAL REPRESENTATIVE:

EDWARDS & ANGELL, LLP, P.O. BOX 9169, BOSTON, MA, 02209

NUMBER OF CLAIMS:

1

EXEMPLARY CLAIM: LINE COUNT: 1057

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

TΤ 355395-09-4P

(photoresist composition containing photoacid labile acrylate and cyclic olefin)

RN355395-09-4 USPATFULL

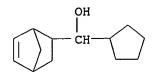
CN 2-Propenoic acid, 2-methyl-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester,

polymer with bicyclo[2.2.1]hept-2-ene, α -

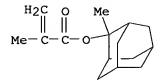
cyclopentylbicyclo[2.2.1]hept-2-ene-2-methanol and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

355395-08-3 CRN CMF C13 H20 O



CRN 177080-67-0 CMF C15 H22 O2



CM 3

CRN 498-66-8 CMF C7 H10



CM 4

CRN 108-31-6 CMF C4 H2 O3



TITLE:

L34 ANSWER 28 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2003:265146 USPATFULL Positive photosensitive composition

INVENTOR(S):

Fujimori, Toru, Shizuoka, JAPAN FUJI PHOTO FILM CO., LTD. (non-U.S. corporation) PATENT ASSIGNEE(S):

			-
	NUMBER	KIND DATE	
PATENT INFORMATION: APPLICATION INFO.:	US 2003186161 US 2002-188224	A1 20031002 A1 20020703	(10)
	NUMBER	DATE	
PRIORITY INFORMATION:	JP 2001-204969 JP 2001-206637	20010705 20010706	
DOCUMENT TYPE: FILE SEGMENT:	JP 2001-287112 Utility APPLICATION	20010920	

LEGAL REPRESENTATIVE: SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W., WASHINGTON, DC, 20037

NUMBER OF CLAIMS: EXEMPLARY CLAIM:

16 1

LINE COUNT:

3188

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

398141-14-5P

(pos. photosensitive composition containing)

RN 398141-14-5 USPATFULL

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, CN polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM

398140-58-4 CRN CMF C13 H20 O2

CM 2

342648-11-7 CRN C13 H22 O2 CMF

3 CM

108-31-6 CRN C4 H2 O3 CMF

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 29 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2003:194414 USPATFULL
TITLE: Positive resist composition
INVENTOR(S): Fujimori, Toru, Shizuoka, JAPAN

Kawabe, Yasumasa, Shizuoka, JAPAN

PATENT ASSIGNEE(S): FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)

NUMBER KIND DATE

PATENT INFORMATION: US 2003134225 A1 20030717 APPLICATION INFO.: US 2002-244070 A1 20020916 (10)

NUMBER DATE

PRIORITY INFORMATION: JP 2001-285180 20010919

JP 2002-563 20020107

DOCUMENT TYPE: Utility
FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W.,

WASHINGTON, DC, 20037

NUMBER OF CLAIMS: 13 EXEMPLARY CLAIM: 1 LINE COUNT: 2741

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 398141-14-5P

(pos. photoresist composition containing)

RN 398141-14-5 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CRN 79-10-7 CMF C3 H4 O2

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INVENTOR(S):

L34 ANSWER 30 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2003:127900 USPATFULL

TITLE:

Novel ester compounds, polymers, resist

compositions and patterning process Nishi, Tsunehiro, Niigata-ken, JAPAN

Hasegawa, Koji, Niigata-ken, JAPAN Watanabe, Takeru, Niigata-ken, JAPAN Kinsho, Takeshi, Niigata-ken, JAPAN Nakashima, Mutsuo, Niigata-ken, JAPAN Tachibana, Seiichiro, Niigata-ken, JAPAN

Hatakeyama, Jun, Niigata-ken, JAPAN

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Co., Ltd., Tokyo, JAPAN (non-U.S.

corporation)

	NUMBER	KIND	DATE	
PATENT INFORMATION:	US 2003088115	A1	20030508	
	US 6670498	В2	20031230	
APPLICATION INFO.:	US 2002-288514	A 1	20021106	(10)

RELATED APPLN. INFO.:

Division of Ser. No. US 2001-842007, filed on 26 Apr

2001, PENDING

DOCUMENT TYPE:

Utility

FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: MILLEN, WHITE, ZELANO & BRANIGAN, P.C., 2200 CLARENDON

BLVD., SUITE 1400, ARLINGTON, VA, 22201

NUMBER OF CLAIMS: 5
EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 2 Drawing Page(s)

LINE COUNT: 1531

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 370089-04-6P

(preparation of ester compound and polymers for photoresist compns. and patterning process)

RN 370089-04-6 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 3-[(1-ethylcyclopentyl)oxy]-1-methyl-3-oxopropyl ester, polymer with 5-(2-bicyclo[2.2.1]hept-5-en-2-ylethyl)dihydro-2(3H)-furanone (9CI) (CA INDEX NAME)

CM 1

CRN 370089-03-5 CMF C13 H18 O2

370088-90-7 CRN CMF C19 H28 O4

L34 ANSWER 31 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2003:112808 USPATFULL

TITLE: INVENTOR(S): Positive photosensitive composition Kodama, Kunihiko, Shizuoka, JAPAN Sato, Kenichiro, Shizuoka, JAPAN

PATENT ASSIGNEE(S):

Fujimori, Toru, Shizuoka, JAPAN FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)

(10)

NUMBER	KIND	DATE
TC 2002077540	λ1	20030424

PATENT INFORMATION:

US 2003077540 20020521

US 2002-150967 **A**1 APPLICATION INFO .:

NUMBER DATE JP 2001-152587 20010522 PRIORITY INFORMATION: JP 2001-155897 20010524 20010528 JP 2001-159060

DOCUMENT TYPE:

Utility APPLICATION FILE SEGMENT:

SUGHRUE MION, PLLC, 2100 PENNSYLVANIA AVENUE, N.W., LEGAL REPRESENTATIVE:

WASHINGTON, DC, 20037

NUMBER OF CLAIMS:

14 1

EXEMPLARY CLAIM:

2952

LINE COUNT: CAS INDEXING IS AVAILABLE FOR THIS PATENT.

398141-14-5P

(resin; pos photoresist composition containing)

RN 398141-14-5 USPATFULL

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, CN polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CRN 342648-11-7 CMF C13 H22 O2

CM3

CRN 108-31-6 CMF C4 H2 O3

4 CM

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 32 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2003:51645 USPATFULL

TITLE:

Novel epoxy compound having alicyclic structure,

polymer, resist composition and patterning

process

INVENTOR(S):

Hasegawa, Koji, Niigata-ken, JAPAN Kinsho, Takeshi, Niigata-ken, JAPAN Watanabe, Takeru, Niigata-ken, JAPAN Nishi, Tsunehiro, Niigata-ken, JAPAN

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Co., Ltd., Tokyo, JAPAN (non-U.S.

corporation)

		NUMBER	KIND	DATE	
PATENT INFORMATION:	US	2003036603	A1	20030220	
APPLICATION INFO.:	US	2002-167393	A1	20020613	(10)

APPLICATION INFO.:

NUMBER DATE

PRIORITY INFORMATION:

JP 2001-179593 20010614

DOCUMENT TYPE: FILE SEGMENT:

Utility

LEGAL REPRESENTATIVE:

APPLICATION MILLEN, WHITE, ZELANO & BRANIGAN, P.C., 2200 CLARENDON

BLVD., SUITE 1400, ARLINGTON, VA, 22201

NUMBER OF CLAIMS:

EXEMPLARY CLAIM: 1 LINE COUNT: 2134

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 478946-03-1P

(oxanorbornene spiro derivative (polymers) for use in chemical amplified resists for photolithog. patterning)

RN 478946-03-1 USPATFULL

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-octahydro-, 1-ethylcyclopentyl ester, polymer with spiro[furan-3(2H),2'-[7]oxabicyclo[2.2.1]hept[5]en]-5(4H)-one (9CI) (CA INDEX NAME)

CM 1

CRN 478945-85-6 CMF C9 H10 O3

CM 2

CRN 279243-82-2 CMF C20 H28 O2

L34 ANSWER 33 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2003:24309 USPATFULL

TITLE:

Modified polycyclic polymers

INVENTOR(S):

Jayaraman, Saikumar, Twinsburg, OH, UNITED STATES Benedikt, George Martin, Solon, OH, UNITED STATES Rhodes, Larry Funderburk, Silver Lake, OH, UNITED

STATES

Vicari, Richard, Strongsville, OH, UNITED STATES Allen, Robert David, San Jose, CA, UNITED STATES

DiPetro, Richard Anthony, San Jose, CA, UNITED STATES Sooriyakumaran, Ratnam, San Jose, CA, UNITED STATES

Wallow, Thomas, Union City, CA, UNITED STATES

PATENT ASSIGNEE(S):

The B.F.Goodrich Company (U.S. corporation)

	NUMBER	KIND	DATE
PATENT INFORMATION:	US 2003018153 US 6794459		20030123 20040921
APPLICATION INFO.: RELATED APPLN. INFO.:	US 2002-224994 Division of Ser. 1999, GRANTED, Pa	No. US	1999-253499, filed on 19 Feb

NUMBER	DATE
	

PRIORITY INFORMATION:

US 1998-75558P 19980223 (60)

DOCUMENT TYPE: FILE SEGMENT:

Utility APPLICATION

LEGAL REPRESENTATIVE:

Nestor W. Shust, Hudak & Shunk Co., L.P.A., Suite 808,

7 West Bowery St., Akron, OH, 44308-1133

NUMBER OF CLAIMS: 16 EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 6 Drawing Page(s)

LINE COUNT: 2100

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 239137-09-8DP, hydrolyzed

(modified polymers having polycyclic side chains for photoresists with

improved hydrophilicity)

RN 239137-09-8 USPATFULL

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-

octahydro-, ethyl ester, polymer with 1,1-dimethylethyl

bicyclo[2.2.1]hept-5-ene-2-carboxylate, ethyl (3-

methylbicyclo[2.2.1]hept-5-en-2-yl)methyl carbonate and trimethylsilyl

bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

CM 1

CRN 239137-00-9 CMF C12 H18 O3

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CM 3

CRN 61615-20-1 CMF C15 H20 O2

CM 4

CRN 56151-01-0 CMF C11 H18 O2 Si 0 C- O- SiMe3

L34 ANSWER 34 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2003:190643 USPATFULL

TITLE: Photoresists, polymers and processes for

microlithography

INVENTOR(S): Feiring, Andrew Edward, Wilmington, DE, United States

Feldman, Jerald, Hockessin, DE, United States

PATENT ASSIGNEE(S): E. I. du Pont de Nemours and Company, Wilmington, DE,

United States (U.S. corporation)

	NUMBER	KIND	DATE	
		-		
PATENT INFORMATION: US	6593058	B1	20030715	
WO	2000017712		20000330	
APPLICATION INFO.: US	2001-806096		20010323	(9)
WO	1999-US21912		19990921	

NUMBER DATE

PRIORITY INFORMATION: US 1998-101502P 19980923 (60) US 1999-120045P 19990212 (60)

DOCUMENT TYPE: Utility

FILE SEGMENT: GRANTED

PRIMARY EXAMINER: Ashton, Rosemary ASSISTANT EXAMINER: Lee, Sin J.

NUMBER OF CLAIMS: 31 EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 1 Drawing Figure(s); 1 Drawing Page(s)

LINE COUNT: 1799

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 262617-09-4P, Norbornene-5-norbornene-2-carboxylic

 $\verb"acid-tetrafluoroethylene copolymer"$

(preparation and use in preparing UV photoresists for microlithog.)

RN 262617-09-4 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, polymer with bicyclo[2.2.1]hept-2-ene and tetrafluoroethene (9CI) (CA INDEX NAME)

CM 1

CRN 498-66-8 CMF C7 H10



CM 2

CRN 120-74-1 CMF C8 H10 O2 CO₂H

CM

CRN 116-14-3 CMF C2 F4

L34 ANSWER 35 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2003:40517 USPATFULL

TITLE:

Photosensitive polymer including copolymer of alkyl

vinyl ether and resist composition containing

the same

INVENTOR(S):

Choi, Sang-jun, Seoul, KOREA, REPUBLIC OF Kim, Hyun-woo, Seongnam, KOREA, REPUBLIC OF

PATENT ASSIGNEE(S):

Samsung Electronics Co., Ltd., Suwon, KOREA, REPUBLIC

OF (non-U.S. corporation)

KIND DATE NUMBER PATENT INFORMATION: US 6517990 B1 20030211 APPLICATION INFO.: US 2000-576053 20000523 (9)

> DATE NUMBER ______

PRIORITY INFORMATION:

KR 2000-2489 20000119 20000419 KR 2000-20603

US 2000-198761P 20000421 (60)

DOCUMENT TYPE: FILE SEGMENT:

Utility GRANTED

1049

PRIMARY EXAMINER:

Ashton, Rosemary

LEGAL REPRESENTATIVE:

Volentine Francos, PLLC

40 NUMBER OF CLAIMS: 1

EXEMPLARY CLAIM:

NUMBER OF DRAWINGS: 2 Drawing Figure(s); 2 Drawing Page(s)

LINE COUNT:

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

350992-45-9P

(chemical amplified photoresists containing alkyl vinyl ether polymers for ArF excimer laser exposure)

350992-45-9 USPATFULL RN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester, CN polymer with 3,4-dihydro-2H-pyran and 2,5-furandione (9CI) (CA INDEX

NAME)

CM 1

CRN 154970-45-3

CMF C12 H18 O2

OBu-t

2 CM

110-87-2 CRN CMF C5 H8 O

3

108-31-6 CRN CMF C4 H2 O3

L34 ANSWER 36 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 21 2003:570079 HCAPLUS

ACCESSION NUMBER:

DOCUMENT NUMBER:

140:383006 TITLE:

AUTHOR(S):

Nonshrinkable photoresists for ArF

lithography

Kim, Jin-Baek; Oh, Tae Hwan; Choi, Jae-Hak; Lee,

CORPORATE SOURCE:

Department of Chemistry, School of Molecular Science (BK21) and Center for Advanced Functional Polymers, Korea Advanced Institute of Science and

Technology, Daejeon, 305-701, S. Korea

SOURCE:

Proceedings of SPIE-The International Society for Optical Engineering (2003), 5039(Pt. 2, Advances in

Resist Technology and Processing XX), 689-697

CODEN: PSISDG; ISSN: 0277-786X

PUBLISHER:

SPIE-The International Society for Optical Engineering

DOCUMENT TYPE: LANGUAGE:

Journal English

683786-03-0P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(nonshrinkable chemical amplified photoresists for ArF lithog.

based on copolymers containing dimethyloxepanone acid labile group)

683786-03-0 HCAPLUS RN

CN 2H-Cyclopenta[b]naphth[2,1-d]oxepin-8-butanoic acid, 2-

[(bicyclo[2.2.1]hept-5-en-2-ylcarbonyl)oxy]hexadecahydro-γ,4a,7atrimethyl-6-oxo-, methyl ester, $(\gamma R, 2R, 4aS, 4bS, 8R, 10aS, 10bR, 12aR)$ -, polymer with 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 683786-01-8 CMF C33 H48 O6

108-31-6 CRN CMF C4 H2 O3

REFERENCE COUNT:

THERE ARE 5 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 22 L34 ANSWER 37 OF 86

ACCESSION NUMBER:

2002:522667 HCAPLUS

DOCUMENT NUMBER:

137:79393

5

TITLE:

Polymers of polycyclic compounds, resist

composition and patterning process

INVENTOR(S):

Tachibana, Seiichiro; Nakashima, Mutsuo; Nishi,

Tsunehiro; Kinsho, Takeshi; Hasegawa, Koji; Watanabe,

Takeru; Hatakeyama, Jun

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Co., Ltd., Japan

SOURCE:

U.S. Pat. Appl. Publ., 38 pp.

CODEN: USXXCO

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
-				
US 2002091215	A1	20020711	US 2001-986274	20011108
US 6660448	B2	20031209		
JP 2002206012	A2	20020726	JP 2001-331910	20011030
TW 536665	В	20030611	TW 2001-90127928	20011109
PRIORITY APPLN. INFO.:			JP 2000-343324 A	20001110
TT 441071-34-7D				

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(polymers of polycyclic compds., resist composition and patterning process)

RN441071-34-7 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 2-ethylbicyclo[2.2.1]hept-2-yl ester, polymer with 3-(2-bicyclo[2.2.1]hept-5-en-2-yl-1hydroxyethyl)dihydro-2(3H)-furanone and 2,5-furandione (9CI) (CA INDEX NAME)

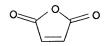
CRN 398488-21-6 CMF C13 H18 O3

CM 2

CRN 330596-01-5 CMF C17 H24 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 38 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 23

ACCESSION NUMBER:

2002:72739 HCAPLUS 136:142610

DOCUMENT NUMBER:

TITLE: INVENTOR(S):

PATENT ASSIGNEE(S): SOURCE:

Positive photoresist composition Sato, Kenichiro; Aoai, Toshiaki Fuji Photo Film Co., Ltd., Japan U.S. Pat. Appl. Publ., 49 pp.

CODEN: USXXCO

DOCUMENT TYPE:

LANGUAGE:

PE: Patent English

FAMILY ACC. NUM. COUNT: 2

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
				_	
US 2002009666	A1	20020124	US 2001-834639		20010416
US 6808860	B2	20041026			
JP 2001296661	A2	20011026	JP 2000-115497		20000417
JP 2002031890	A2	20020131	JP 2000-215574		20000717
JP 3444844	B2	20030908			
JP 2002040662	A2	20020206	JP 2000-231670		20000731
PRIORITY APPLN. INFO.:			JP 2000-115497	Α	20000417
			JP 2000-215574	Α	20000717
			JP 2000-231670	Α	20000731

IT 392310-13-3P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material

CM 1

CRN 392310-12-2 CMF C14 H18 O4

CM 2

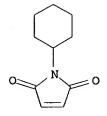
CRN 383196-79-0 CMF C12 H20 O2

CM 3

CRN 22497-08-1 CMF C10 H16 O

CM 4

CRN 1631-25-0 CMF C10 H13 N O2



L34 ANSWER 39 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 24

ACCESSION NUMBER:

2002:975674 HCAPLUS

DOCUMENT NUMBER:

138:63818

TITLE:

Novel oxanorbornene spiro derivatives and their

polymers for use as resists for photolithographic patterning

INVENTOR(S):

Hasegawa, Koji; Kaneo, Takeshi; Watanabe, Takeshi;

Nishi, Tsunehiro

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Industry Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 39 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

LANGUAGE:

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002371080	A2	20021226	JP 2001-179593	20010614
US 2003036603	A1	20030220	us 2002-167393	20020613
PRIORITY APPLN. INFO.:			JP 2001-179593 A	20010614
	242 D D 2 M	100.00010		

OTHER SOURCE(S):

MARPAT 138:63818

478946-03-1P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

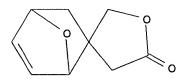
(oxanorbornene spiro derivative (polymers) for use in chemical amplified resists for photolithog. patterning)

478946-03-1 HCAPLUS RN

1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8a-CN octahydro-, 1-ethylcyclopentyl ester, polymer with spiro[furan-3(2H),2'-[7]oxabicyclo[2.2.1]hept[5]en]-5(4H)-one (9CI) (CA INDEX NAME)

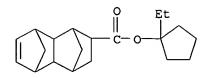
CM 1

CRN 478945-85-6 CMF C9 H10 O3



CM 2

CRN 279243-82-2 CMF C20 H28 O2



L34 ANSWER 40 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 25

ACCESSION NUMBER: 2002:904532 HCAPLUS

DOCUMENT NUMBER: 137:391087

TITLE: Positive-working photoresist compositions

containing specific resin and specific acid-generator

INVENTOR(S): Sato, Kenichiro; Kodama, Kunihiko PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 105 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 2

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
JP 2002341539	A2	20021127	JP 2001-149620		20010518
US 2003008241	A1	20030109	US 2002-93411		20020311
US 6777160	B2	20040817			
TW 538317	В	20030621	TW 2002-91104604		20020312
PRIORITY APPLN. INFO.:			JP 2001-68849	Α	20010312
			JP 2001-68850	Α	20010312
			JP 2001-149620	Α	20010518

IT 398141-14-5P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resin; pos.-working photoresist compns.)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 41 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 26

ACCESSION NUMBER:

2002:848227 HCAPLUS

DOCUMENT NUMBER:

137:360309

TITLE:

Radiation-sensitive positive resist

compositions showing wide defocus latitude and less

particle generation on storage

INVENTOR(S):

Kodama, Kunihiko; Sato, Kenichiro Fuji Photo Film Co., Ltd., Japan

PATENT ASSIGNEE(S): SOURCE:

Jpn. Kokai Tokkyo Koho, 90 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

4

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
JP 2002323767	A2	20021108	JP 2001-157366		20010525
US 2003017415	A 1	20030123	US 2002-79414		20020222
us 6858370	B2	20050222			
TW 548523	В	20030821	TW 2002-91103178		20020222
PRIORITY APPLN. INFO.:			JP 2001-48602	Α	20010223
			JP 2001-48783	Α	20010223
			JP 2001-48784	Α	20010223
			JP 2001-48880	Α	20010223
			JP 2001-157366	Α	20010525
			JP 2001-157367	Α	20010525

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses) (radiation-sensitive pos. resist compns. showing wide defocus latitude and less particle generation on storage)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 3

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 42 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 27

ACCESSION NUMBER:

2002:848220 HCAPLUS

DOCUMENT NUMBER:

137:360306

TITLE:

Radiation-sensitive positively working photosensitive

composition

INVENTOR(S):
PATENT ASSIGNEE(S):

Kodama, Kunihiko; Sato, Kenichiro Fuji Photo Film Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 92 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

LANGUAGE: FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
JP 2002323758	A2	20021108	JP 2001-157367		20010525
US 2003017415	A1	20030123	US 2002-79414		20020222
บร 6858370	B2	20050222			
PRIORITY APPLN. INFO.:			JP 2001-48783	Α	20010223
			JP 2001-48602	Α	20010223
•			JP 2001-48784	Α	20010223
			JP 2001-48880	Α	20010223
			JP 2001-157366	Α	20010525
			JP 2001-157367	Α	20010525

IT 398141-14-5P 405509-24-2P 474510-67-3P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(radiation-sensitive pos. working photosensitive composition for high resolution and storage stability)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CRN 79-10-7 CMF C3 H4 O2

RN 405509-24-2 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1-hydroxy-1-methylethyl ester, polymer with 2,5-furandione, 1-methyl-1-tricyclo[3.3.1.13,7]dec-1-ylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and tetrahydro-5-oxo-3-furanyl bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

CM 1

CRN 405509-23-1 CMF C11 H16 O3

CM 2

CRN 398140-70-0 CMF C12 H14 O4

CM 3

CRN 328087-76-9 CMF C21 H30 O2

CRN 108-31-6 CMF C4 H2 O3

RN 474510-67-3 HCAPLUS
CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 3hydroxytricyclo[3.3.1.13,7]dec-1-yl ester, polymer with
1-bicyclo[2.2.1]hept-5-en-2-yl-2-methyl-2-(4-methylcyclohexyl)-1propanone, 5-ethoxy-3a,4,5,6,7,7a-hexahydro-4,7-methano-1H-indene and
2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 474510-66-2 CMF C18 H28 O

CM 2

CRN 331866-92-3 CMF C18 H24 O3

CM 3

CRN 53018-26-1 CMF C12 H18 O

CM 4

CRN 108-31-6 CMF C4 H2 O3



INVENTOR(S):

L34 ANSWER 43 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 28

ACCESSION NUMBER: 2002:792710 HCAPLUS

DOCUMENT NUMBER: 137:317922

TITLE: Positive photoresist compositions offering

sharp patterns Sato, Kenichiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 85 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

DATE APPLICATION NO. PATENT NO. KIND DATE _____ ____ 20010502 A2 20021018 JP 2001-135245 JP 2002303984 JP 2001-22010 20010130 PRIORITY APPLN. INFO.: Α

OTHER SOURCE(S): MARPAT 137:317922

IT 398141-14-5P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. photoresist compns. offering sharp patterns)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CRN 108-31-6 CMF C4 H2 O3

CM 4

79-10-7 CRN CMF C3 H4 O2

L34 ANSWER 44 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 29

ACCESSION NUMBER:

2002:673047 HCAPLUS

DOCUMENT NUMBER:

SOURCE:

137:224108

TITLE:

Storage-stable excimer laser-sensitive

positive-working photosensitive compositions with

reduced pattern variation on defocusing

INVENTOR(S):

PATENT ASSIGNEE(S):

Kodama, Kunihiko; Sato, Kenichiro Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 86 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese LANGUAGE:

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
JP 2002251012	A2	20020906	JP 2001-48784		20010223
US 2003017415	A1	20030123	US 2002-79414		20020222
US 6858370	B2	20050222			
TW 548523	В	20030821	TW 2002-91103178		20020222
PRIORITY APPLN. INFO.:			JP 2001-48602	Ą	20010223
			JP 2001-48783	Ą	20010223
			JP 2001-48784	4	20010223
			JP 2001-48880 A	4	20010223
			JP 2001-157366 A	Ą	20010525
			JP 2001-157367	A	20010525

IT 398141-14-5P

RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(chemical amplified storage-stable excimer laser-sensitive pos.

photoresists with reduced pattern variation on defocusing)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 45 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 30

ACCESSION NUMBER:

2002:673045 HCAPLUS

DOCUMENT NUMBER:

137:224107

TITLE:

Chemically amplified positive-working far-UV photoresist compositions suitable for halftone

phase-shift masks

INVENTOR(S):

Sato, Kenichiro; Uenishi, Kazuya Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 104 pp.

PATENT ASSIGNEE(S): SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

LANGUAGE:

JT: 1

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

JP 2002251011 A2 20020906 JP 2001-48782 20010223 PRIORITY APPLN. INFO.: JP 2001-48782 20010223

OTHER SOURCE(S):

IT

MARPAT 137:224107

398141-14-5P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(chemical amplified pos.-working far-UV photoresists suitable for halftone phase-shift masks)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 46 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 31

2002:592336 HCAPLUS ACCESSION NUMBER:

DOCUMENT NUMBER: 137:147763

Chemically amplified positive-working TITLE:

photoresist composition providing fine

resolution patterns

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

SOURCE:

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 94 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002221796	A2	20020809	JP 2001-18868	20010126
ORITY APPLN. INFO.:			JP 2001-18868	20010126

PRIO OTHER SOURCE(S):

MARPAT 137:147763

398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses) (in chemical amplified pos.-working photoresist composition for far-UV exposure)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

2 CM

CRN 342648-11-7 CMF C13 H22 O2

CM 3

108-31-6 CRN CMF C4 H2 O3

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 47 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 32

ACCESSION NUMBER:

2002:566567 HCAPLUS

DOCUMENT NUMBER:

137:132103

TITLE:

SOURCE:

Positive-working **photoresist** composition

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 93 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002214787 PRIORITY APPLN. INFO.:	A2	20020731	JP 2001-13298	20010122 20010122

IT 398141-14-5P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resin in pos.-working photoresist composition)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 48 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 33

ACCESSION NUMBER:

2002:566566 HCAPLUS

DOCUMENT NUMBER:

137:132102

TITLE:

Positive-working photoresist composition

INVENTOR(S):

Fujimori, Toru

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

SOURCE:

Jpn. Kokai Tokkyo Koho, 78 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

1

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002214786	A2	20020731	JP 2001-10481	20010118
PRIORITY APPLN. INFO.:			JP 2001-10481	20010118
IT 398141-14-5P				

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resin in pos.-working photoresist composition)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 49 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 34

ACCESSION NUMBER:

2002:538441 HCAPLUS

DOCUMENT NUMBER:

137:116950

TITLE:

SOURCE:

Chemically amplified far-UV positive **photoresists** compositions with improved exposure margin and defocus latitude

INVENTOR(S):

Sato, Kenichiro

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 81 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent Japanese

1

LANGUAGE:
FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002202607	A2	20020719	JP 2000-402246	20001228

OTHER SOURCE(S):

MARPAT 137:116950

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses) (far-UV pos. photoresists having sulfonium and iodonium photoacid generators with improved exposure margin and defocus latitude)

398141-14-5 HCAPLUS RN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, CN polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM

398140-58-4 CRN C13 H20 O2

CM 2

342648-11-7 CRN C13 H22 O2 CMF

3 CM

CRN 108-31-6 CMF C4 H2 O3

CM

79-10-7 CRN C3 H4 O2 CMF

L34 ANSWER 50 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 35

ACCESSION NUMBER: 2002:538440 HCAPLUS

DOCUMENT NUMBER:

137:116949

TITLE:

Storage-stable chemically amplified far-UV positive

photoresists compositions with good

sensitivity and no aggregation

INVENTOR(S):

Sato, Kenichiro

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 81 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

SOURCE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002202606	A2	20020719	JP 2000-402245	20001228
PRIORITY APPLN. INFO.:			JP 2000-402245	20001228

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses) (storage-stable far-UV pos. photoresist compns. in solvents with good solubility)

398141-14-5 HCAPLUS RN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, CN polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

398140-58-4 CRN CMF C13 H20 O2

CM

CRN 342648-11-7 C13 H22 O2 CMF

3 CM

CRN 108-31-6 CMF C4 H2 O3

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 51 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 36

ACCESSION NUMBER:

2002:539335 HCAPLUS

DOCUMENT NUMBER:

137:101423

TITLE:

Storage-stable chemically amplified far-UV positive

photoresist compositions suitable for

half-tone phase-shift photomasks

INVENTOR(S):

Sato, Kenichiro

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan Jpn. Kokai Tokkyo Koho, 80 pp.

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

SOURCE:

Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002202605	A2	20020719	JP 2000-402244	20001228
PRIORITY APPLN. INFO.:			JP 2000-402244	20001228

OTHER SOURCE(S):

MARPAT 137:101423

IT 398141-14-5

RL: TEM (Technical or engineered material use); USES (Uses) (storage-stable far-UV pos. **photoresists** containing triphenylsulfonium photoacid generators for half-tone phase-shift photomasks)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA_INDEX_NAME)

CM :

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 52 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 37

ACCESSION NUMBER: 2002:237124 HCAPLUS

DOCUMENT NUMBER: 136:286589

TITLE: Positive-working chemically amplified

photoresist composition containing specific

acid-sensitive resin and specific nitrogen-containing

compound for semiconductor device fabrication Fujimori, Toru; Kawabe, Yasumasa; Nakao, Hajime

INVENTOR(S): Fujimori, Toru; Kawabe, Yasumasa; PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 92 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
					
JP 2002090987	A2	20020327	JP 2001-209543		20010710
US 2002155383	A1	20021024	US 2001-902793		20010712
US 6692897	B2	20040217			
PRIORITY APPLN. INFO.	;		JP 2000-211642	Α	20000712
OTHER SOURCE(S):	MARPAT	136:286589			
IT 398141-14-5P 405					
RL: SPN (Syntheti	ic prepara	tion); TEM	(Technical or engine	ered	material
use); PREP (Prepa	aration);	USES (Uses)			

(resin in pos.-working photoresist composition)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CRN 398140-58-4 CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

RN 405509-24-2 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1-hydroxy-1-methylethyl ester, polymer with 2,5-furandione, 1-methyl-1-tricyclo[3.3.1.13,7]dec-1-ylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and tetrahydro-5-oxo-3-furanyl bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

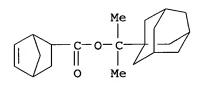
CM 1

CRN 405509-23-1 CMF C11 H16 O3

CRN 398140-70-0 CMF C12 H14 O4

CM 3

CRN 328087-76-9 CMF C21 H30 O2



CM 4

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 53 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 38

ACCESSION NUMBER:

2002:904448 HCAPLUS

DOCUMENT NUMBER:

138:9656

TITLE:

Positive photosensitive composition

INVENTOR(S):

Kodama, Kunihiko; Sato, Kenichiro; Fujimori, Toru

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE:

Eur. Pat. Appl., 145 pp. CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1260864	A1 B1	20021127	EP 2002-11516	20020522
	H, DE, DK	, ES, FR,	GB, GR, IT, LI, LU, NL, CY, AL, TR	SE, MC, PT,

JP 2002351077	A2	20021204	JP	2001-152587		20010522
JP 2002351079	A2	20021204	JР	2001-155897		20010524
JP 2002351063	A2	20021204	JP	2001-159060		20010528
us 2003077540	A1	20030424	US	2002-150967		20020521
PRIORITY APPLN. INFO.:			JP	2001-152587	Α	20010522
			JP	2001-155897	Α	20010524
			JР	2001-159060	Α	20010528

OTHER SOURCE(S): MARPAT 138:9656

IT 398141-14-5P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resin; pos photoresist composition containing)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CM 2

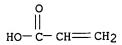
CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2



REFERENCE COUNT:

9 THERE ARE 9 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 54 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 39

ACCESSION NUMBER:

2002:272837 HCAPLUS

DOCUMENT NUMBER:

136:310309

TITLE:

Polymers with cyclopentane rings in or adjacent to the

chains, resist composition and patterning

process

INVENTOR(S):

Nishi, Tsunehiro; Nakashima, Mutsuo; Hasegawa, Koji;

Tachibana, Seiichiro; Kinsho, Takeshi; Watanabe,

Takeru; Hatakeyama, Jun

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Co., Ltd., Japan

SOURCE:

Eur. Pat. Appl., 47 pp. CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
EP 1195390	A1	20020410	EP 2001-307791	20010913
EP 1195390	B1	20041208		
R: AT, BE,	CH, DE, Di	K, ES, FR,	GB, GR, IT, LI, LU, I	NL, SE, MC, PT,
IE, SI,	LT, LV, F	I, RO		
JP 2002161116	A2	20020604	JP 2001-269745	20010906
TW 557304	В	20031011	TW 2001-90122771	20010913
US 2002061463	A1	20020523	US 2001-951523	20010914
US 6673515	B2	20040106		
PRIORITY APPLN. INFO.	:		JP 2000-279164	A 20000914
TT 400000 CE OD				

IT 409093-65-8P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(polymers with cyclopentane rings in or adjacent to the chains for resists patternable by UV or electron beams)

RN 409093-65-8 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-ethylbicyclo[2.2.1]hept-2-yl ester, polymer with 5-(2-bicyclo[2.2.1]hept-5-en-2-ylethyl)dihydro-2(3H)-furanone and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 370089-03-5 CMF C13 H18 O2

CM 2

CRN 330595-98-7 CMF C13 H20 O2

CRN 108-31-6 CMF C4 H2 O3

REFERENCE COUNT: 9 THERE ARE 9 CITED REFERENCES AVAILABLE FOR THIS

RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 55 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 40

ACCESSION NUMBER:

2002:119352 HCAPLUS

DOCUMENT NUMBER:

136:175472

TITLE:

Positive photosensitive composition for

photofabrication using deep UV ray

INVENTOR(S):

Kodama, Kunihiko; Aoai, Toshiaki

PATENT ASSIGNEE(S):

Fuji Photo Film Co., Ltd., Japan

SOURCE:

Eur. Pat. Appl., 120 pp.
CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

	PA'	ENT	NO.			KIN	D	DATE		i	APP	LICAT	ION	NO.		D.	ATE	
							-									-		
	ΕP	1179	750			A1		2002	0213	1	EΡ	2001-	1177	96		2	0010	802
		R:	AT,	BE,	CH,	DE,	DK,	ES,	FR,	GB,	GR	, IT,	LI,	LU,	NL,	SE,	MC,	PT,
			ΙE,	SI,	LT,	LV,	FI,	RO										
	JP	2002	1229	94		A2		2002	0426	,	JP	2001-	1886	70		2	0010	621
	US	2002	0519	33		A1		2002	0502	Į	US	2001-	9216	91		2	0010	806
	US	6492	091			B2		2002	1210									
PRIO	RIT!	APP	LN.	INFO	.:					,	JP	2000-	2400	59		A 2	0000	808
TITO	200		44 -	_														

IT 398141-14-5P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(resin; deep UV photofabrication pos. **photoresist** composition containing)

RN 398141-14-5 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl 2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

CRN 398140-58-4 CMF C13 H20 O2

CRN 342648-11-7 CMF C13 H22 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

REFERENCE COUNT:

13 THERE ARE 13 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 56 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2002:301718 USPATFULL

TITLE:

Polymeric compound and resin composition for

photoresist

INVENTOR(S):

Funaki, Yoshinori, Himeji-shi, JAPAN Tsutsumi, Kiyoharu, Himeji-shi, JAPAN Takaragi, Akira, Himeji-shi, JAPAN

	NUMBER	KIND	DATE	
PATENT INFORMATION:	US 2002169266	A1	20021114	
	US 6552143	B2	20030422	
APPLICATION INFO.:	US 2001-937910	A1	20011019	(9)
	WO 2001-JP515		20010126	

NUMBER DATE

PRIORITY INFORMATION:

JP 2000-24527

20000201

DOCUMENT TYPE:

Utility APPLICATION

FILE SEGMENT: LEGAL REPRESENTATIVE:

BIRCH STEWART KOLASCH & BIRCH, PO BOX 747, FALLS

CHURCH, VA, 22040-0747

NUMBER OF CLAIMS:

5

EXEMPLARY CLAIM:

1

LINE COUNT: 3139
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 353289-59-5P

(polymeric compound for photoresist and resin composition for photoresist)

RN 353289-59-5 USPATFULL

CN Tricyclo[3.3.1.13,7]decane-1-carboxylic acid, 3-[(1-oxo-2-propenyl)oxy]-,

1,1-dimethylethyl ester, polymer with 2,5-furandione, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate and

3a, 4, 7, 7a-tetrahydro-4, 7-methanoisobenzofuran-1(3H)-one (9CI) (CA INDEX

NAME)

CM 1

CRN 251563-20-9 CMF C18 H26 O4

CM 2

CRN 216581-76-9 CMF C13 H18 O3

CM 3

CRN 85718-44-1 CMF C9 H10 O2

CM 4

CRN 108-31-6



L34 ANSWER 57 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2002:279949 USPATFULL

TITLE:

Positive resist composition

Fujimori, Toru, Shizuoka, JAPAN INVENTOR(S):

Kawabe, Yasumasa, Shizuoka, JAPAN

Nakao, Hajime, Shizuoka, JAPAN

PATENT ASSIGNEE(S):

FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)

NUMBER KIND DATE US 2002155383 A1 20021024 PATENT INFORMATION: US 6692897 20040217 B2 US 2001-902793 20010712 A1 (9) APPLICATION INFO .:

> DATE NUMBER _____

PRIORITY INFORMATION:

JP 2000-211642 20000712

DOCUMENT TYPE:

FILE SEGMENT:

Utility

APPLICATION

LEGAL REPRESENTATIVE:

SUGHRUE, MION, ZINN,, MACPEAK & SEAS, PLLC, 2100

Pennsylvania Avenue, NW, Washington, DC, 20037-3213

NUMBER OF CLAIMS:

17

EXEMPLARY CLAIM:

1

LINE COUNT:

2009

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

398141-14-5P 405509-24-2P

(resin in pos.-working photoresist composition)

398141-14-5 USPATFULL RN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, CN

polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl

2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM

398140-58-4 CRN CMF C13 H20 O2

CM 2

CRN 342648-11-7 CMF C13 H22 O2

CRN 108-31-6 CMF C4 H2 O3

CM 4

CRN 79-10-7 CMF C3 H4 O2

RN 405509-24-2 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1-hydroxy-1-methylethyl ester, polymer with 2,5-furandione, 1-methyl-1-tricyclo[3.3.1.13,7]dec-1-ylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and tetrahydro-5-oxo-3-furanyl bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

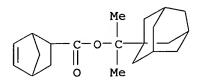
CM 1

CRN 405509-23-1 CMF C11 H16 O3

CM 2

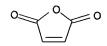
CRN 398140-70-0 CMF C12 H14 O4

CRN 328087-76-9 CMF C21 H30 O2



CM 4

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 58 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2002:172456 USPATFULL

TITLE:

Novel photoresist monomer having hydroxy

group and carboxy group, copolymer thereof and

photoresist composition using the same

INVENTOR(S):

Lee, Geun Su, Ichon-shi, KOREA, REPUBLIC OF Koh, Cha Won, Ichon-shi, KOREA, REPUBLIC OF Jung, Jae Chang, Ichon-shi, KOREA, REPUBLIC OF Jung, Min Ho, Ichon-shi, KOREA, REPUBLIC OF Baik, Ki Ho, Ichon-shi, KOREA, REPUBLIC OF

PATENT ASSIGNEE(S):

Hyundai Electronics Industries Co., Ltd., Ichon-shi,

KOREA, REPUBLIC OF (non-U.S. corporation)

		NUMBER	KIND	DATE	
PATENT INFORMATION:	US	2002091216	A1	20020711	
	US	6586619	B2	20030701	
APPLICATION INFO.:	US	2002-79753	A1	20020219	(10)

RELATED APPLN. INFO.: Division of Ser. No. US 1999-383861, filed on 26 Aug

1999, PENDING

		NUMBER	DATE
PRIORITY	INFORMATION:	KR 1998-34694	19980826
		KR 1998-39079	19980921

DOCUMENT TYPE: Utility
FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: TOWNSEND AND TOWNSEND AND CREW, LLP, TWO EMBARCADERO

CENTER, EIGHTH FLOOR, SAN FRANCISCO, CA, 94111-3834

NUMBER OF CLAIMS: 40
EXEMPLARY CLAIM: 1
LINE COUNT: 979

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 260065-43-8P

(preparation of photoresist copolymer using new photoresist-monomer for photoresist composition with submicron resolution)

RN 260065-43-8 USPATFULL

CN 7-Oxabicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono(5-hydroxypentyl) ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,1-dimethylethyl hydrogen bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylate and 2,5-furandione (9CI) (CA

CRN 260065-28-9 CMF C13 H18 O6

CM 2

CRN 76198-01-1 CMF C13 H18 O4

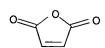
CM 3

CRN 498-66-8 CMF C7 H10



CM 4

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 59 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2002:119480 USPATFULL

TITLE:

Polymer, resist composition and patterning

process

INVENTOR(S):

Nishi, Tsunehiro, Nakakubiki-gun, JAPAN Nakashima, Mutsuo, Nakakubiki-gun, JAPAN Tachibana, Seiichiro, Nakakubiki-gun, JAPAN Kinsho, Takeshi, Nakakubiki-gun, JAPAN Hasegawa, Koji, Nakakubiki-gun, JAPAN Watanabe, Takeru, Nakakubiki-gun, JAPAN Hatakeyama, Jun, Nakakubiki-gun, JAPAN

PATENT ASSIGNEE(S): Shin-Etsu Chemical Co., Ltd., Tokyo, JAPAN (non-U.S.

corporation)

NUMBER DATE

PRIORITY INFORMATION: JP 2000-279164 20000914

DOCUMENT TYPE: Utility FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: MILLEN, WHITE, ZELANO & BRANIGAN, P.C., 2200 CLARENDON

BLVD., SUITE 1400, ARLINGTON, VA, 22201

NUMBER OF CLAIMS: 7
EXEMPLARY CLAIM: 1
LINE COUNT: 1766

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 409093-65-8P

(polymers with cyclopentane rings in or adjacent to the chains for resists patternable by UV or electron beams)

RN 409093-65-8 USPATFULL

CN 2-Propenoic acid, 2-methyl-, 2-ethylbicyclo[2.2.1]hept-2-yl ester, polymer with 5-(2-bicyclo[2.2.1]hept-5-en-2-ylethyl)dihydro-2(3H)-furanone and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 370089-03-5 CMF C13 H18 O2

CM 2

CRN 330595-98-7 CMF C13 H20 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3



INVENTOR(S):

L34 ANSWER 60 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2002:99037 USPATFULL

TITLE:

Positive photosensitive composition Kodama, Kunihiko, Shizuoka, JAPAN

Aoai, Toshiaki, Shizuoka, JAPAN

PATENT ASSIGNEE(S):

FUJI PHOTO FILM CO., LTD. (non-U.S. corporation)

NUMBER KIND DATE _____ ______

PATENT INFORMATION: US 2002051933

A1 20020502 US 6492091 B2 20021210

US 2001-921691 APPLICATION INFO.:

A1 20010806 (9)

NUMBER DATE

PRIORITY INFORMATION:

JP 2000-240059 20000808

DOCUMENT TYPE:

Utility

FILE SEGMENT:

APPLICATION

LEGAL REPRESENTATIVE:

SUGHRUE, MION, ZINN, MACPEAK & SEAS, PLLC, 2100 Pennsylvania Avenue, N.W., Washington, DC, 20037

NUMBER OF CLAIMS:

EXEMPLARY CLAIM:

1

LINE COUNT:

2260 CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 398141-14-5P

(resin; deep UV photofabrication pos. photoresist composition containing)

RN 398141-14-5 USPATFULL

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylpropyl ester, CN

polymer with 2,5-furandione, 1-methyl-1-(4-methylcyclohexyl)ethyl

2-propenoate and 2-propenoic acid (9CI) (CA INDEX NAME)

CM 1

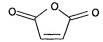
CRN 398140-58-4

CMF C13 H20 O2

CM

CRN 342648-11-7 CMF C13 H22 O2

CRN 108-31-6 CMF C4 H2 O3



CM 4

CRN 79-10-7 CMF C3 H4 O2

INVENTOR(S):

L34 ANSWER 61 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2002:12648 USPATFULL

TITLE: Novel ester compounds, polymers, resist

compositions and patterning process Nishi, Tsunehiro, Niigata-ken, JAPAN

Hasegawa, Koji, Niigata-ken, JAPAN Watanabe, Takeru, Niigata-ken, JAPAN Kinsho, Takeshi, Niigata-ken, JAPAN Nakashima, Mutsuo, Niigata-ken, JAPAN Tachibana, Seiichiro, Niigata-ken, JAPAN

Hatakeyama, Jun, Niigata-ken, JAPAN

PATENT ASSIGNEE(S): Shin-Etsu Chemical Co., Ltd., Tokyo, JAPAN (non-U.S.

corporation)

APPLICATION INFO.: US 2001-842007 Al 20010426 (9)

NUMBER DATE

PRIORITY INFORMATION: JP 2000-127532 20000427

DOCUMENT TYPE: Utility FILE SEGMENT: APPLICATION

LEGAL REPRESENTATIVE: MILLEN, WHITE, ZELANO & BRANIGAN, P.C., 2200 CLARENDON

BLVD., SUITE 1400, ARLINGTON, VA, 22201

NUMBER OF CLAIMS: 5 EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 2 Drawing Page(s)

LINE COUNT: 1531

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 370089-04-6P

(preparation of ester compound and polymers for photoresist compns. and patterning process)

RN 370089-04-6 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 3-[(1-ethylcyclopentyl)oxy]-1-methyl-3-oxopropyl ester, polymer with 5-(2-bicyclo[2.2.1]hept-5-en-2-ylethyl)dihydro-2(3H)-furanone (9CI) (CA INDEX NAME)

CRN 370089-03-5 CMF C13 H18 O2

CM 2

CRN 370088-90-7 CMF C19 H28 O4

L34 ANSWER 62 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2002:239130 USPATFULL

TITLE:

Modified polycyclic polymers

INVENTOR(S):

Jayaraman, Saikumar, Twinsburg, OH, United States Benedikt, George Martin, Solon, OH, United States Rhodes, Larry Funderburk, Silver Lake, OH, United

States

Vicari, Richard, Strongsville, OH, United States Allen, Robert David, San Jose, CA, United States DiPietro, Richard Anthony, San Jose, CA, United States

Sooriyakumaran, Ratnam, San Jose, CA, United States

Wallow, Thomas, Union City, CA, United States

PATENT ASSIGNEE(S):

The B.F. Goodrich Company, Charlotte, NC, United States

(U.S. corporation)

International Business Machines Corp., Armonk, NY,

United States (U.S. corporation)

	NUMBER	KIND	DATE	
US	6451945	B1	20020917	
US :	1999-253499		19990219	(9)

PATENT INFORMATION: APPLICATION INFO.:

> NUMBER DATE

PRIORITY INFORMATION:

US 1998-75558P 19980223 (60)

DOCUMENT TYPE: Utility FILE SEGMENT: GRANTED

PRIMARY EXAMINER:

Moore, Margaret G.

LEGAL REPRESENTATIVE:

Dunlap, Thoburn T., Hudak & Shunk Co., LPA

NUMBER OF CLAIMS: 1

5

EXEMPLARY CLAIM: NUMBER OF DRAWINGS:

6 Drawing Figure(s); 6 Drawing Page(s)

LINE COUNT:

1954

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

239137-09-8DP, hydrolyzed

(modified polymers having polycyclic side chains for photoresists with improved hydrophilicity)

RN 239137-09-8 USPATFULL

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8aoctahydro-, ethyl ester, polymer with 1,1-dimethylethyl

bicyclo[2.2.1]hept-5-ene-2-carboxylate, ethyl (3-

methylbicyclo[2.2.1]hept-5-en-2-yl)methyl carbonate and trimethylsilyl bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

CRN 239137-00-9 CMF C12 H18 O3

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CM 3

CRN 61615-20-1 CMF C15 H20 O2

CM 4

CRN 56151-01-0 CMF C11 H18 O2 Si

L34 ANSWER 63 OF 86 USPATFULL on STN

ACCESSION NUMBER:

INVENTOR(S):

2002:188208 USPATFULL

TITLE:

Photoresist monomer, polymer thereof and

photoresist composition containing it

Jung, Min Ho, Kyoungki-do, KOREA, REPUBLIC OF Jung, Jae Chang, Kyoungki-do, KOREA, REPUBLIC OF Lee, Geun Su, Kyoungki-do, KOREA, REPUBLIC OF

Baik, Ki Ho, Kyoungki-do, KOREA, REPUBLIC OF Hyundai Electronics Industries Co., Ltd., KOREA, PATENT ASSIGNEE(S):

REPUBLIC OF (non-U.S. corporation)

NUMBER KIND PATENT INFORMATION: US 6426171 20020730 B1 20000728 APPLICATION INFO.: US 2000-627714 (9)

> NUMBER DATE

PRIORITY INFORMATION: KR 1999-31303 19990730

KR 1999-31304 19990730

DOCUMENT TYPE: Utility GRANTED FILE SEGMENT:

PRIMARY EXAMINER: Ashton, Rosemary

LEGAL REPRESENTATIVE: Townsend and Townsend and Crew LLP

NUMBER OF CLAIMS:

EXEMPLARY CLAIM:

NUMBER OF DRAWINGS: 0 Drawing Figure(s); 0 Drawing Page(s)

LINE COUNT:

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

332138-97-3P

(copolymer in deep UV-sensitive resist composition)

RN 332138-97-3 USPATFULL

Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-(1-CN pyrrolidinyl)ethyl] ester, polymer with bicyclo[2.2.1]hept-5-ene-2carboxylic acid, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2carboxylate, 2,5-furandione and 2-hydroxyethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

CM

CRN 332138-78-0 CMF C15 H21 N O4

CM 2

CRN 154970-45-3 CMF C12 H18 O2

3 CM

CRN 37503-42-7 CMF C10 H14 O3

CRN 120-74-1 CMF C8 H10 O2

CM 5

CRN 108-31-6 CMF C4 H2 O3

L34 ANSWER 64 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2002:174921 USPATFULL

TITLE: Resist compositions and patterning process INVENTOR(S): Nishi, Tsunehiro, Nakakubiki-gun, JAPAN Ohsawa, Youichi, Nakakubiki-gun, JAPAN

Hatakeyama, Jun, Nakakubiki-gun, JAPAN

PATENT ASSIGNEE(S): Shin-Etsu Chemical Co., Ltd., Tokyo, JAPAN (non-U.S.

corporation)

		NUMBER	KIND	DATE	
PATENT INFORMATION:	US	6420085	B1	20020716	
APPLICATION INFO.:	US	2000-663830		20000915	(9)

NUMBER DATE

PRIORITY INFORMATION: JP 1999-263257 19990917

DOCUMENT TYPE: Utility FILE SEGMENT: GRANTED

PRIMARY EXAMINER: Ashton, Rosemary

LEGAL REPRESENTATIVE: Millen, White, Zelano & Branigan, P.C.

NUMBER OF CLAIMS: 14
EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 0 Drawing Figure(s); 0 Drawing Page(s)

LINE COUNT: 1276

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 330596-00-4

(resist compns. comprising sulfonium photoacid generator and copolymers for ArF laser lithog. and patterning process)

RN 330596-00-4 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1-ethylcyclopentyl ester, polymer with 1-ethylcyclopentyl 2-methyl-2-propenoate and 2,5-furandione (9CI) (CA INDEX NAME)

CRN 279243-69-5 CMF C15 H22 O2

2 CM

CRN . 266308-58-1 CMF C11 H18 O2

3 CM

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 65 OF 86 USPATFULL on STN

ACCESSION NUMBER:

2002:152742 USPATFULL

TITLE:

Photoresist monomer having hydroxy group and

carboxy group, copolymer thereof and

photoresist composition using the same

INVENTOR(S):

Lee, Geun Su, Kyoungki-do, KOREA, REPUBLIC OF Koh, Cha Won, Kyoungki-do, KOREA, REPUBLIC OF Jung, Jae Chang, Kyoungki-do, KOREA, REPUBLIC OF Jung, Min Ho, Kyoungki-do, KOREA, REPUBLIC OF Baik, Ki Ho, Kyoungki-do, KOREA, REPUBLIC OF Hyundai Electronics Industries Co., Ltd., KOREA,

PATENT ASSIGNEE(S):

REPUBLIC OF (non-U.S. corporation)

		NUMBER	KIND	DATE	
PATENT INFORMATION:	US	6410670	B1	20020625	
APPLICATION INFO.:	US	1999-383861		19990826	(9)

NUMBER DATE

PRIORITY INFORMATION: KR 1998-34694 19980826 KR 1998-39079 19980921

DOCUMENT TYPE: Utility FILE SEGMENT: GRANTED PRIMARY EXAMINER: Wu, David W. ASSISTANT EXAMINER: Zalukaeva, Tanya LEGAL REPRESENTATIVE: Townsend and Townsend and Crew LLP NUMBER OF CLAIMS: 9

1

NUMBER OF CLAIMS: EXEMPLARY CLAIM:

NUMBER OF DRAWINGS: 0 Drawing Figure(s); 0 Drawing Page(s)

LINE COUNT: 879

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 260065-43-8P

(preparation of photoresist copolymer using new photoresist-monomer for photoresist composition with submicron resolution)

RN 260065-43-8 USPATFULL

7-Oxabicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono(5-hydroxypentyl) ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,1-dimethylethyl hydrogen bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 260065-28-9 CMF C13 H18 O6

CM 2

CRN 76198-01-1 CMF C13 H18 O4

CM 3

CRN 498-66-8 CMF C7 H10



CM 4

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 66 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2002:136731 USPATFULL

TITLE: Cross-linker monomer comprising double bond and

photoresist copolymer containing the same

INVENTOR(S): Lee, Geun Su, Kyoungki-do, KOREA, REPUBLIC OF Jung, Jae Chang, Kyoungki-do, KOREA, REPUBLIC OF

Baik, Ki Ho, Kyoungki-do, KOREA, REPUBLIC OF

PATENT ASSIGNEE(S): Hyundai Electronics Industries Co., Ltd., KOREA,

REPUBLIC OF (non-U.S. corporation)

NUMBER KIND DATE

PATENT INFORMATION: US 6403281 B1 20020611

APPLICATION INFO.: US 2000-643460 20000822 (9)

PRIORITY INFORMATION: KR 1999-35046 19990823

DOCUMENT TYPE: Utility FILE SEGMENT: GRANTED

PRIMARY EXAMINER: Ashton, Rosemary

LEGAL REPRESENTATIVE: Townsend and Townsend and Crew LLP

NUMBER OF CLAIMS: 2 EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 6 Drawing Figure(s); 6 Drawing Page(s)

LINE COUNT: 530

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 328068-00-4P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tertbutylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-2,5-hexanediol diacrylate

(preparation of photoresist copolymer containing crosslinking monomer with double bond)

RN 328068-00-4 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,4-dimethyl-1,4-butanediyl di-2-propenoate, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 250583-69-8 CMF C16 H24 O5

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CRN 85996-28-7 CMF C12 H18 O4

CM 4

CRN 498-66-8 CMF C7 H10



CM 5

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 67 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 41

ACCESSION NUMBER:

2003:156547 HCAPLUS

DOCUMENT NUMBER:

138:385816

TITLE:

Synthesis of a novel methacrylate,

(1,4-dioxa-8-methacrylate amide spiro [4,5] decane)

monomer and its co-polymerization with

t-butyl-3 α -methacryloxy-7 α , 12 α -

dihydroxy-5β cholan-24-oate for 193 nm

photoresist

AUTHOR(S):

Karak, Niranjan; Ko, Jong Sung; Kim, Jin-Baek

CORPORATE SOURCE: Department of Chemistry, Korea Advanced Institute of

Sciences and Technology, Taejon, 305701, S. Korea

Journal of Polymer Materials (2002), 19(4), 365-372

CODEN: JOPME8; ISSN: 0970-0838

PUBLISHER:

LANGUAGE:

SOURCE:

Oxford & IBH Publishing Co. Pvt. Ltd.

DOCUMENT TYPE:

Journal English

IT 525558-73-0P

RL: PRP (Properties); SPN (Synthetic preparation); PREP (Preparation)

(synthesis of 1,4-dioxa-8-azospiro[4.5]decane 8-methacrylamide monomer and its copolymn. with tert-butyl-3α-methacryloxy-7α,12α- dihydroxy-5β cholan-24-oate for 193 nm photoresist)
525558-73-0 HCAPLUS

RN 525558-73-0 HCAPLUS
CN Cholan-24-oic acid, 7,12-dihydroxy-3-[(2-methyl-1-oxo-2-propenyl)oxy]-,
 1,1-dimethylethyl ester, (3α,5β,7α,12α)-, polymer
 with 2,5-furandione, 8-(2-methyl-1-oxo-2-propenyl)-1,4-dioxa-8 azaspiro[4.5]decane and α-[2,2,2-trifluoro-1,1 bis(trifluoromethyl)ethoxy]bicyclo[2.2.1]hept-5-ene-2-methanol (9CI) (CIINDEX NAME)

CM 1

CRN 525558-70-7 CMF C12 H11 F9 O2

CM 2

CRN 525558-69-4 CMF C32 H52 O6

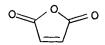
Absolute stereochemistry.

CM 3

CRN 525558-68-3 CMF C11 H17 N O3

CM 4

CRN 108-31-6



REFERENCE COUNT:

17 THERE ARE 17 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 68 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 42

ACCESSION NUMBER:

2001:582183 HCAPLUS

DOCUMENT NUMBER:

135:160158

TITLE:

Polymeric compound for photoresist and resin

composition for photoresist

INVENTOR(S):

Funaki, Yoshinori; Tsutsumi, Kiyoharu; Takaragi, Akira

PATENT ASSIGNEE(S):

Daicel Chemical Industries, Ltd., Japan

SOURCE:

PCT Int. Appl., 120 pp.

SOURCE.

CODEN: PIXXD2

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

I	PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
7	WO 2001057597	A1	20010809	WO 2001-JP515		20010126
	W: KR, US RW: DE, FR, GB					
į	JP 2001215703	A2	20010810	JP 2000-24527		20000201
I	EP 1172694	A1	20020116	EP 2001-949041		20010126.
	R: DE, FR, GB					
7	rw 538311	В	20030621	TW 2001-90101862		20010131
· t	JS 2002169266	A 1	20021114	US 2001-937910		20011019
τ	US 6552143	В2	20030422			
τ	JS 2004006189	A1	20040108	us 2003-375129		20030228
τ	US 6806335	В2	20041019			
PRIOR	ITY APPLN. INFO.:			JP 2000-24527	Α	20000201
				WO 2001-JP515	W	20010126
				US 2001-937910	Α1	20011019

IT 353289-59-5P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(polymeric compound for **photoresist** and resin composition for

photoresist)

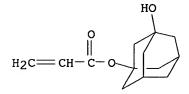
RN 353289-59-5 HCAPLUS

CN Tricyclo[3.3.1.13,7]decane-1-carboxylic acid, 3-[(1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester, polymer with 2,5-furandione, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate and 3a,4,7,7a-tetrahydro-4,7-methanoisobenzofuran-1(3H)-one (9CI) (CA INDEX NAME)

CM 1

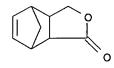
CRN 251563-20-9 CMF C18 H26 O4

CRN 216581-76-9 CMF C13 H18 O3



CM 3

CRN 85718-44-1 CMF C9 H10 O2



CM

CRN 108-31-6 CMF C4 H2 O3



REFERENCE COUNT:

19 THERE ARE 19 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 69 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 43

ACCESSION NUMBER:

2001:713843 HCAPLUS

DOCUMENT NUMBER:

135:264568

TITLE:

Photosensitive polymer including copolymer of alkyl

vinyl ether and resist composition

containing the same

INVENTOR(S):

Choi, Sang-jun; Kim, Hyun-woo

PATENT ASSIGNEE(S): SOURCE:

Samsung Electronics Co., Ltd., S. Korea U.S. Pat. Appl. Publ., 20 pp., Cont.-in-part of U.S.

Ser. No. 576,053.

CODEN: USXXCO

DOCUMENT TYPE:

Patent English

LANGUAGE: FAMILY ACC. NUM. COUNT:

3

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE US 2001024763 A1 20010927 US 2001-764150 20010119 B2 US 6673513 20040106 20010811 Α KR 2000-20603 20000419 KR 2001076138 US 6517990 B1 20030211 US 2000-576053 20000523 A1 US 2003194643 20031016 US 2003-392931 20030321 B2 US 6833230 20041221 A1 US 2004137363 20040715 US 2003-704977 20031112

KR 2000-2489 A 20000119 PRIORITY APPLN. INFO.: KR 2000-20603 A 20000419 US 2000-198761P 20000421 Ρ US 2000-576053 A2 20000523 US 2001-764150 A2 20010119 A 20020621

IT 350992-45-9P

RL: POF (Polymer in formulation); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (synthesis of photosensitive copolymer of alkyl vinyl ether and maleic anhydride for resist composition)

KR 2002-34998

RN 350992-45-9 HCAPLUS

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester, CN polymer with 3,4-dihydro-2H-pyran and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 154970-45-3 CMF C12 H18 O2

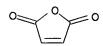
2 CM

CRN 110-87-2 CMF C5 H8 O



3 CM

CRN 108-31-6 C4 H2 O3 CMF



THERE ARE 21 CITED REFERENCES AVAILABLE FOR THIS REFERENCE COUNT: 21 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 44 L34 ANSWER 70 OF 86

ACCESSION NUMBER:

2001:534446 HCAPLUS

DOCUMENT NUMBER:

135:129569

TITLE:

Chemically amplified photoresist

compositions containing alkyl vinyl ether polymers for

ArF excimer laser exposure

INVENTOR(S):

Choi, Sang Joon; Kim, Hyun Woo

PATENT ASSIGNEE(S):

Samsung Electronics Co., Ltd., S. Korea

SOURCE:

Jpn. Kokai Tokkyo Koho, 21 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 3

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE		
JP 2001200016	A2	20010724	JP 2001-12171	20010119		
KR 2001076138	Α	20010811	KR 2000-20603	20000419		
EP 1120689	-A2	20010801	EP 2001-300418	20010118		
EP 1120689	A3	20010808				
R: AT, BE, CH,	DE, DK	, ES, GB, GR	, IT, LI, LU, NL, SE, M	C, PT, IE,		
SI, LT, LV,	FI, RO	ı				
PRIORITY APPLN. INFO.:			KR 2000-2489 A	20000119		
			KR 2000-20603 A	20000419		

IT 350992-45-9P

RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(chemical amplified **photoresists** containing alkyl vinyl ether polymers for ArF excimer laser exposure)

RN 350992-45-9 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1,1-dimethylethyl ester, polymer with 3,4-dihydro-2H-pyran and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 154970-45-3 CMF C12 H18 O2

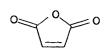
CM 2

CRN 110-87-2 CMF C5 H8 O



CM 3

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 71 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 45

ACCESSION NUMBER:

2001:238005 HCAPLUS

DOCUMENT NUMBER:

134:287851

TITLE: Monomer for copolymer in deep UV-sensitive

resist composition for semiconductor device fabrication and method for preparation thereof

Chung, Min Ho; Chung, Jae Chang; Lee, Geun Soo; Paek, INVENTOR(S):

Hyundai Electronics Industries Co., Ltd., S. Korea; PATENT ASSIGNEE(S):

Hynix Semiconductor Co., Ltd.

Jpn. Kokai Tokkyo Koho, 34 pp. SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE:

Patent

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE		
				-		
JP 2001089539	A2	20010403	JP 2000-231613		20000731	
JP 3515949	B2	20040405				
KR 2001011773	Α	20010215	KR 1999-31303		19990730	
KR 2001011774	Α	20010215	KR 1999-31304		19990730	
US 6426171	B1	20020730	US 2000-627714		20000728	
PRIORITY APPLN. INFO.:			KR 1999-31303	Α	19990730	
			KR 1999-31304	Α	19990730	

OTHER SOURCE(S):

MARPAT 134:287851

TT 332138-97-3P

> RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(copolymer in deep UV-sensitive resist composition)

332138-97-3 HCAPLUS RN

Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-(1-CN pyrrolidinyl)ethyl] ester, polymer with bicyclo[2.2.1]hept-5-ene-2carboxylic acid, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate, 2,5-furandione and 2-hydroxyethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate (9CI) (CA INDEX NAME)

CM 1

CRN 332138-78-0 CMF C15 H21 N O4

2 CM

154970-45-3 CRN C12 H18 O2 CMF

CM 3

CRN 37503-42-7

120-74-1 CRN C8 H10 O2



CM 5

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 72 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 46

ACCESSION NUMBER:

DOCUMENT NUMBER:

2001:217905 HCAPLUS 134:259208

TITLE:

Photosensitive polymer and resist

composition containing it

INVENTOR(S):

Choi, Sang Joon

PATENT ASSIGNEE(S):

Samsung Electronics Co., Ltd., S. Korea

SOURCE:

Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF Patent

DOCUMENT TYPE:

LANGUAGE:

Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	DATE APPLICATION NO.			
JP 2001081140	A2	20010327	JP 2000-231005	20000731		
US 6270942	B1	20010807	US 2000-539138	20000330		
PRIORITY APPLN. INFO.:			KR 1999-31059 A	19990729		
TM 004440 48 05						

IT 331449-17-3P

> RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(photoresist composition containing polymer with alicyclic backbone and photoacid generator)

331449-17-3 HCAPLUS RN

Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, bis(ethoxymethyl) ester, CN polymer with 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 331449-14-0

CRN 108-31-6 CMF C4 H2 O3

L34 ANSWER 73 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 47

ACCESSION NUMBER:

2001:796274 HCAPLUS

DOCUMENT NUMBER:

135:336914

TITLE:

Ester compounds, polymers, resist

compositions and patterning process

INVENTOR(S):

Hasegawa, Koji; Nishi, Tsunehiro; Kinsho, Takeshi;

Watanabe, Takeru; Nakashima, Mutsuo; Tachibana,

Seiichiro; Hatakeyama, Jun

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Co., Ltd., Japan

SOURCE:

Eur. Pat. Appl., 45 pp. CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PA	PATENT NO.					ND DATE			APPLICATION NO.						DATE		
EP	EP 1149825			149825		A2 2001103		1031	EP 2001-303867				20010427				
EP	1149	825			A3		20030326										
	R:	AT,	BE,	CH,	DE,	DK,	ES,	FR,	GB,	GF	R, IT,	LI,	LU,	NL,	SE	, MC,	PT,
		IE,	SI,	LT,	LV,	FI,	, RO										
JP	2002	0126	22		A2		2002	0115		JΡ	2001-	1240	05			20010	423
US	2002	0070	31		A1		2002	0117		US	2001-	8420	07			20010	426
US	6531	627			B2		2003	0311									
US	2003	0881	15		A 1		2003	0508		US	2002-	2885	14			20021	106
บร	6670	498			В2		2003	1230									
PRIORIT	Y APP	LN.	INFO	. :						JP	2000-	1275	32		Α :	20000	427
										US	2001-	8420	07		A3 :	20010	426
OTHER SO	OURCE	(S):			MARI	TAS	135:	3369	14								

IT 370089-04-6P

> RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(preparation of ester compound and polymers for photoresist compns. and patterning process)

370089-04-6 HCAPLUS RN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 3-[(1-ethylcyclopentyl)oxy]-1-CN methyl-3-oxopropyl ester, polymer with 5-(2-bicyclo[2.2.1]hept-5-en-2ylethyl)dihydro-2(3H)-furanone (9CI) (CA INDEX NAME)

CM 1 CRN 370089-03-5 CMF C13 H18 O2

CM 2

CRN 370088-90-7 CMF C19 H28 O4

L34 ANSWER 74 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 48

ACCESSION NUMBER:

2001:631979 HCAPLUS

DOCUMENT NUMBER:

135:187722

TITLE:

Photoresist compositions comprising novel

copolymers

INVENTOR(S):

Barclay, George G.; Caporale, Stefan J.; Yueh, Wang;

Mao, Zhibiao; Mattia, Joseph

PATENT ASSIGNEE(S):

Shipley Company L.L.C., USA

SOURCE:

Eur. Pat. Appl., 21 pp.

CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

1	PAT	ENT	NO.			KIN	D	DATE	DATE			LICAT	DATE					
-	EP 1128213				A2		20010829		- F	EP 2001-		-3016	13	20010222				
]	ΕP	1128	213			A3		2003	1119				·					
		R:	AT,	BE,	CH,	DE,	DK,	, ES,	FR,	GB,	GR	, IT,	LI,	LU,	ΝL,	SE,	MC,	PT,
			ΙE,	SI,	LT,	LV,	FI	, RO										
1	US	6777	157			В1		2004	0817	Ţ	JS	2000-	-5678	14		2	0000	509
	TW	5847	81			В		2004	0421	7	W.	2001-	-9010	4232		2	0010	223
	JP	2001	2966	63		A2		2001	1026		JΡ	2001-	-5068	1		2	0010	226
1	US	2003	2157	42		A 1		2003	1120	Ţ	JS	2003-	-4085	22		2	0030	407
1	US	6849	381			В2		2005	0201									
PRIOR	ITY	APP	LN.	INFO	. :					τ	JS	2000-	-1853	45P		P 2	0000	226
										τ	JS	2000-	-5678	14		A 2	0000	509
TITO 9	255	205	00 4	_						•		• -	,			_		

IT 355395-09-4P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(photoresist composition containing photoacid labile acrylate and cyclic olefin)

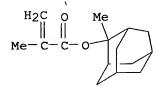
RN 355395-09-4 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 2-methyltricyclo[3.3.1.13,7]dec-2-yl ester,
 polymer with bicyclo[2.2.1]hept-2-ene, α cyclopentylbicyclo[2.2.1]hept-2-ene-2-methanol and 2,5-furandione (9CI)
 (CA INDEX NAME)

CM 1

CRN 355395-08-3 CMF C13 H20 O

CRN 177080-67-0 CMF C15 H22 O2



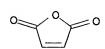
CM 3

CRN 498-66-8 CMF C7 H10



CM 4

CRN 108-31-6 CMF C4 H2 O3



L34 ANSWER 75 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 49

ACCESSION NUMBER:

2001:208018 HCAPLUS

DOCUMENT NUMBER:

134:259202

TITLE:

Resist compositions comprising sulfonium

photoacid generator for ArF excimer laser lithography

DATE

and patterning process

INVENTOR(S):
PATENT ASSIGNEE(S):

Nishi, Tsunehiro; Ohsawa, Youichi; Hatakeyama, Jun

Shin-Etsu Chemical Co., Ltd., Japan

SOURCE:

Eur. Pat. Appl., 36 pp. CODEN: EPXXDW

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO.

EP 1085377 A1 20010321 EP 2000-307915 20000913 R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO

JP 2001083695 A2 20010330 JP 1999-263257 19990917 US 6420085 B1 20020716 US 2000-663830 20000915 PRIORITY APPLN. INFO.: JP 1999-263257 A 19990917

OTHER SOURCE(S): MARPAT 134:259202

IT 330596-00-4

RL: PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)

(resist compns. comprising sulfonium photoacid generator and copolymers for ArF laser lithog. and patterning process)

RN 330596-00-4 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, 1-ethylcyclopentyl ester, polymer with 1-ethylcyclopentyl 2-methyl-2-propenoate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 279243-69-5 CMF C15 H22 O2

CM 2

CRN 266308-58-1 CMF C11 H18 O2

CM 3

CRN 108-31-6 CMF C4 H2 O3

REFERENCE COUNT: 4 THERE ARE 4 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 76 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 50

ACCESSION NUMBER:

2001:150535 HCAPLUS

DOCUMENT NUMBER:

134:200535

TITLE:

Crosslinking monomer containing double bond and

photoresist copolymer containing the same

INVENTOR(S):
PATENT ASSIGNEE(S):

Lee, Geun Su; Jung, Jae Chang; Baik, Ki Ho Hyundai Electronics Industries Co., Ltd., Ichon, S.

Korea

SOURCE: Ger. Offen., 16 pp.

CODEN: GWXXBX

Patent

DOCUMENT TYPE: LANGUAGE:

LANGUAGE: German FAMILY ACC. NUM. COUNT: 2

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
DE 10040963	A 1	20010301	DE 2000-10040963	20000822
KR 2001018905	Α	20010315	KR 1999-35046	19990823
GB 2354004	A1	20010314	GB 2000-19436	20000809
GB 2354004	B2	20040114		
JP 2001106737	A2	20010417	JP 2000-252762	20000823
PRIORITY APPLN. INFO.:			KR 1999-35046	19990823

IT 328068-00-4P, Mono-2-ethyl-2-(hydroxymethyl)-butylbicyclo-[2.2.1]-hept-5-ene-2,3-dicarboxylate-maleic acid anhydride-norbornene-tert-butylbicyclo-[2.2.1]-hept-5-ene-2-carboxylate-2,5-hexanediol diacrylate copolymer

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(preparation of **photoresist** copolymer containing crosslinking monomer with double bond)

RN 328068-00-4 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono[2-ethyl-2-(hydroxymethyl)butyl] ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,4-dimethyl-1,4-butanediyl di-2-propenoate, 1,1-dimethylethyl bicyclo[2.2.1]hept-5-ene-2-carboxylate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 250583-69-8 CMF C16 H24 O5

CM 2

CRN 154970-45-3 CMF C12 H18 O2

CM 3

CRN 85996-28-7 CMF C12 H18 O4

CRN 498-66-8 C7 H10 CMF



5 CM

CRN 108-31-6 CMF C4 H2 O3

L34 ANSWER 77 OF 86 USPATFULL on STN

2001:214807 USPATFULL ACCESSION NUMBER:

Photoresist cross-linker and TITLE:

photoresist composition comprising the same INVENTOR(S):

Jung, Jae Chang, Kyoungki-do, Korea, Republic of

Kong, Keun Kyu, Kwangju, Korea, Republic of Kim, Jin Soo, Daejeon, Korea, Republic of Baik, Ki Ho, Kyoungki-do, Korea, Republic of

Hyundai Electronics Industries Co., Ltd., Korea, PATENT ASSIGNEE(S):

Republic of (non-U.S. corporation)

	NUMBER	KIND	DATE	
PATENT INFORMATION: U	S 6322948	B1	20011127	
APPLICATION INFO.: U	S 2000-499231		20000207	(9)

DATE NUMBER 19990210 PRIORITY INFORMATION: KR 1999-4593

DOCUMENT TYPE: Utility

GRANTED FILE SEGMENT:

PRIMARY EXAMINER: Ashton, Rosemary

Townsend and Townsend and Crew LLP LEGAL REPRESENTATIVE:

NUMBER OF CLAIMS: 10 EXEMPLARY CLAIM: 1

10 Drawing Figure(s); 5 Drawing Page(s) NUMBER OF DRAWINGS:

555 LINE COUNT:

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

288619-55-6P

(crosslinking agent; norbornene derivative polymers as crosslinking agents

for photoresists and their use in semiconductor device fabrication)

RN 288619-55-6 USPATFULL

2-Propenoic acid, polymer with 5-(dimethoxymethyl)bicyclo[2.2.1]hept-2-ene CN

and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 69448-18-6 CMF C10 H16 O2

CM 2

CRN 108-31-6 CMF C4 H2 O3

CM 3

CRN 79-10-7 CMF C3 H4 O2

L34 ANSWER 78 OF 86 USPATFULL on STN

ACCESSION NUMBER: 2001:179213 USPATFULL

TITLE: Polycyclic copolymer compositions

INVENTOR(S): Goodall, Brian Leslie, Baton Rouge, LA, United States

McIntosh, III, Lester Howard, Cuyahoga Falls, OH,

United States

PATENT ASSIGNEE(S): The B. F. Goodrich Company, Brecksville, OH, United

States (U.S. corporation)

	NUMBER	KIND	DATE	
- -				
	5 6303724 5 1999-345286	B1	20011016 19990630	(9)

NUMBER DATE

PRIORITY INFORMATION: US 1998-91361P 19980701 (60)

DOCUMENT TYPE: Utility
FILE SEGMENT: GRANTED
PRIMARY EXAMINER: Wu, David W.
ASSISTANT EXAMINER: Cheung, William

LEGAL REPRESENTATIVE: Dunlap, Thoburn T. Hudak & Shunk Co., L.P.A.

NUMBER OF CLAIMS: 8
EXEMPLARY CLAIM: 1

NUMBER OF DRAWINGS: 3 Drawing Figure(s); 3 Drawing Page(s)

LINE COUNT: 1296

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

```
(polycyclic copolymer compns.)
    254751-22-9 USPATFULL
RN
    2-Propenoic acid, methyl ester, polymer with 5-butylbicyclo[2.2.1]hept-2-
CN
       ene (9CI) (CA INDEX NAME)
    CM
         1
    CRN 22094-81-1
    CMF C11 H18
       Bu-n
         2
    CM
    CRN 96-33-3
    CMF C4 H6 O2
MeO-C-CH-CH2
L34 ANSWER 79 OF 86 USPATFULL on STN
                       2001:147641 USPATFULL
ACCESSION NUMBER:
TITLE:
                       Ester compounds, polymers, resist
                       compositions and patterning process
                       Kinsho, Takeshi, Nakakubiki-gun, Japan
INVENTOR(S):
                       Nishi, Tsunehiro, Nakakubiki-gun, Japan
                       Kurihara, Hideshi, Usui-gun, Japan
                       Nakashima, Mutsuo, Nakakubiki-gun, Japan
                       Hasegawa, Koji, Nakakubiki-gun, Japan
                       Watanabe, Takeru, Nakakubiki-gun, Japan
PATENT ASSIGNEE(S):
                       Shin-Etsu Chemical Co., Ltd., Tokyo, Japan (non-U.S.
                       corporation)
                            NUMBER
                                       KIND DATE
                       US 6284429
                                        B1
                                               20010904
PATENT INFORMATION:
                       US 2000-512108
                                               20000224 (9)
APPLICATION INFO.:
                              NUMBER DATE
                        JP 1999-47406
                                          19990225
PRIORITY INFORMATION:
                       JP 1999-174945
                                          19990622
DOCUMENT TYPE:
                       Utility
FILE SEGMENT:
                       GRANTED
                       Ashton, Rosemary E.
PRIMARY EXAMINER:
                       Millen, White, Zelano & Branigan, P.C
LEGAL REPRESENTATIVE:
NUMBER OF CLAIMS:
                       19
EXEMPLARY CLAIM:
                       1
                       2016
LINE COUNT:
CAS INDEXING IS AVAILABLE FOR THIS PATENT.
IT 290809-04-0P
        (novel ester compds., polymers, resist compns. and patterning process)
     290809-04-0 USPATFULL
RN
     Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, (1R,2R,4S)-2-
CN
       ethylbicyclo[2.2.1]hept-2-yl ester, rel-, polymer with
       rel-(3aR, 4S, 5R, 7S, 7aR)-5-ethyloctahydro-4,7-methano-1H-inden-5-yl
       2-methyl-2-propenoate and 2,5-furandione (9CI) (CA INDEX NAME)
```

254751-22-9P

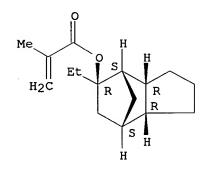
CRN 290808-30-9 CMF C17 H24 O2

Relative stereochemistry.

CM 2

CRN 271598-65-3 CMF C16 H24 O2

Relative stereochemistry.



CM 3

CRN 108-31-6 CMF C4 H2 O3

L34 ANSWER 80 OF 86 USPATFULL on STN

2001:125716 USPATFULL ACCESSION NUMBER:

TITLE: Photosensitive polymer having cyclic backbone and

resist composition comprising the same

INVENTOR(S):

Choi, Sang-jun, Seoul, Korea, Republic of Samsung Electronics Co., LTD, Korea, Republic of PATENT ASSIGNEE(S):

(non-U.S. corporation)

NUMBER KIND DATE US 6270942 PATENT INFORMATION: В1 20010807 APPLICATION INFO.: US 2000-539138 20000330 (9)

> DATE NUMBER

PRIORITY INFORMATION: KR 1999-31059 19990729 DOCUMENT TYPE: Utility FILE SEGMENT: GRANTED

PRIMARY EXAMINER: Ashton, Rosemary E. LEGAL REPRESENTATIVE: Mills & Onello LLP

NUMBER OF CLAIMS: 11 EXEMPLARY CLAIM: 4 LINE COUNT: 497

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IT 331449-17-3P

(photoresist composition containing polymer with alicyclic backbone and photoacid generator)

RN 331449-17-3 USPATFULL

CN Bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, bis(ethoxymethyl) ester, polymer with 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 331449-14-0 CMF C15 H22 O6

CM 2

CRN 108-31-6 CMF C4 H2 O3

L34 ANSWER 81 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 51

ACCESSION NUMBER: 2000:210534 HCAPLUS

DOCUMENT NUMBER: 132:258158.

TITLE: Photoresist for microlithography

INVENTOR(S): Feiring, Andrew Edward; Feldman, Jerald PATENT ASSIGNEE(S): E. I. Du Pont de Nemours & Co., USA

SOURCE: PCT Int. Appl., 54 pp.

CODEN: PIXXD2

DOCUMENT TYPE: Patent LANGUAGE: English

FAMILY ACC. NUM. COUNT: 3

PATENT INFORMATION:

PATENT NO.						KIND DATE			i	APPL	DATE							
					,													
WO 2000017712						A 1	A1 20000330			1	WO 1	999-		19990921				
		W:	ΑE,	AL,	AU,	BA,	BB,	BG,	BR,	CA,	CN,	CR,	CU,	CZ,	EE,	GD,	GE,	HR,
			HU,	ID,	IL,	IN,	IS,	JP,	KP,	KR,	LC,	LK,	LR,	LT,	LV,	MG,	MK,	MN,
			MX,	NO,	NZ,	PL,	RO,	SG,	SI,	SK,	SL,	TR,	TT,	UA,	US,	UZ,	VN,	ΥU,
			ZA,	AM,	ΑZ,	BY,	KG,	ΚZ,	MD,	RU,	ТJ,	TM						
		RW:	GH,	GM,	KE,	LS,	MW,	SD,	SL,	SZ,	TZ,	UG,	ZW,	ΑT,	BE,	CH,	CY,	DE,
			DK,	ES,	FI,	FR,	GB,	GR,	IE,	IT,	LU,	MC,	NL,	PT,	SE,	BF,	ВJ,	CF,
			CG,	CI,	CM,	GΑ,	GN,	GW,	ML,	MR,	NE,	SN,	TD,	TG				
AU 9960560				A 1		2000	0410	١.	AU 1	999-	6056	0		1	9990	921		

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EP 1999-969504
      EP 1131677
                                  20010912
                                                                      19990921
                            A1
             AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,
              IE, SI, LT, LV, FI, RO
                                              JP 2000-571312
                                                                      19990921
      JP 2002525683
                                  20020813
                            T2
                                              US 2001-806096
                                                                      20010323
      US 6593058
                            В1
                                  20030715
                                              US 2002-108935
                                                                      20020327
      US 2004023150
                                  20040205
                           A1
      US 6849377
                            B2
                                  20050201
      US 2004023152
                            Α1
                                  20040205
                                              US 2003-437760
                                                                      20030514
PRIORITY APPLN. INFO.:
                                              US 1998-101502P
                                                                      19980923
                                              US 1999-120045P
                                                                   Ρ
                                                                      19990212
                                                                      19990921
                                              WO 1999-US21912
                                                                   W
                                              US 2001-806096
                                                                   A2 20010323
                                              US 2001-280268P
                                                                      20010330
                                                                   P
      262617-09-4P, Norbornene-5-norbornene-2-carboxylic
 IT
      acid-tetrafluoroethylene copolymer
      RL: SPN (Synthetic preparation); TEM (Technical or engineered material
      use); PREP (Preparation); USES (Uses)
         (preparation and use in preparing UV photoresists for microlithog.)
```

RN 262617-09-4 HCAPLUS

CN Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, polymer with

bicyclo[2.2.1]hept-2-ene and tetrafluoroethene (9CI) (CA INDEX NAME)

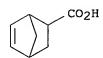
CM. 1

CRN 498-66-8 CMF C7 H10



2 CM

120-74-1 CRN CMF C8 H10 O2



CM3

CRN 116-14-3 CMF C2 F4

REFERENCE COUNT:

THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS 3 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 52 L34 ANSWER 82 OF 86

ACCESSION NUMBER:

2000:34921 HCAPLUS

DOCUMENT NUMBER:

132:93814

TITLE:

Polycyclic copolymer compositions

INVENTOR(S):

Goodall, Brian L.; McIntosh, Lester H., III

PATENT ASSIGNEE(S): The B.F. Goodrich Company, USA

Patent

SOURCE: PCT Int. Appl., 55 pp.

CODEN: PIXXD2

English LANGUAGE: FAMILY ACC. NUM. COUNT: 1

DOCUMENT TYPE:

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. _____ -----WO 1999-US13903 WO 2000001747 A1 20000113 19990618 W: AL, AM, AU, AZ, BA, BB, BG, BR, BY, CA, CN, CZ, EE, GE, HU, ID, IL, IS, JP, KE, KG, KR, KZ, LC, LK, LR, LS, LT, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, RO, RU, SD, SG, SI, SK, SL, TJ, TM, TR, TT, UA, UG, UZ, VN, YU, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM RW: GH, GM, KE, LS, MW, SD, SL, SZ, UG, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG AU 9948263 20000124 AU 1999-48263 A1 EP 1999-931841 20010425 EP 1093480 A1 19990618 R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, FI JP 2000-558145 JP 2002519487 T2 20020702 19990618 В1 20011016 US 1999-345286 19990630 US 6303724 PRIORITY APPLN. INFO.: US 1998-91361P P 19980701 W 19990618

WO 1999-US13903

IT 254751-22-9P

> RL: IMF (Industrial manufacture); PREP (Preparation) (polycyclic copolymer compns.)

254751-22-9 HCAPLUS RN

2-Propenoic acid, methyl ester, polymer with 5-butylbicyclo[2.2.1]hept-2-CN ene (9CI) (CA INDEX NAME)

CM 1

CRN 22094-81-1 CMF C11 H18

CM 2

CRN 96-33-3 CMF C4 H6 O2

REFERENCE COUNT: 3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 83 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 53

ACCESSION NUMBER:

2000:587079 HCAPLUS

DOCUMENT NUMBER:

133:185543

TITLE:

Monomers for photoresist crosslinking agents, photoresist crosslinking agents, photoresist compositions, patterning of photoresist compositions, and semiconductor devices

INVENTOR(S): Chung, Jae Chang; Kong, Geun Kyu; Kim, Jin Soo; Paek,

Ki Ho

PATENT ASSIGNEE(S): Hyundai Electronics Industries Co., Ltd., S. Korea

SOURCE: Jpn. Kokai Tokkyo Koho, 27 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
JP 2000231191	A2	20000822	JP 2000-32228		20000209
KR 2000055772	Α	20000915	KR 1999-4593		19990210
TW 528929	В	20030421	TW 2000-89101778		20000202
US 6322948	B1	20011127	US 2000-499231		20000207
PRIORITY APPLN. INFO.:			KR 1999-4593	Α	19990210
OMITED COLLEGE (C).	343 D D 3 M	122.105542			

OTHER SOURCE(S): MARPAT 133:185543

IT 288619-55-6P

RL: IMF (Industrial manufacture); MOA (Modifier or additive use); PEP (Physical, engineering or chemical process); PREP (Preparation); PROC (Process); USES (Uses)

(crosslinking agent; norbornene derivative polymers as crosslinking agents for **photoresists** and their use in semiconductor device fabrication)

RN 288619-55-6 HCAPLUS

CN 2-Propenoic acid, polymer with 5-(dimethoxymethyl)bicyclo[2.2.1]hept-2-ene and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 69448-18-6 CMF C10 H16 O2

CM 2

CRN 108-31-6 CMF C4 H2 O3

CM 3

CRN 79-10-7 CMF C3 H4 O2

HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 54 L34 ANSWER 84 OF 86

ACCESSION NUMBER:

2000:608477 HCAPLUS

DOCUMENT NUMBER:

133:215453

TITLE:

Novel ester compounds, polymers, resist

compositions and patterning process

INVENTOR(S):

Kinsho, Takeshi; Nishi, Tsunehiro; Kurihara, Hideshi;

Nakashima, Mutsuo; Hasegawa, Koji; Watanabe, Takeru

PATENT ASSIGNEE(S):

Shin-Etsu Chemical Co., Ltd., Japan

Eur. Pat. Appl., 71 pp.

SOURCE: -

DOCUMENT TYPE:

CODEN: EPXXDW

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PA	TENT	NO.			KIND DAT			TE APPLICAT:			:ATI	ON N	10.		DATE		
EP	1031		A1 20000830			EP 2000-301523						2000022					
	R:	AT,	BE,	CH,	DE,	DK,	ES,	FR,	GB, G	R, I	Τ,	LI,	LU,	NL,	SE	, MC,	PT,
		ΙE,	SI,	LT,	LV,	FI,	RO										
JР	2000	3096	11		A2		2000	1107	JP	199	9-1	7494	15			19990	622
KR	2000	0581	67		Α		2000	0925	KR	200	00-8	963				20000	224
บร	6284	429			B1		2001	0904	US	200	0-5	1210	80			20000	224
PRIORIT	Y APP	LN.	INFO	.:					JP	199	9-4	7406	5	1	A	19990	225
									JP	199	9-1	7494	15	7	A	19990	622

IT 290809-04-0P

RL: POF (Polymer in formulation); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (novel ester compds., polymers, resist compns. and patterning process)

290809-04-0 HCAPLUS RN

CN

Bicyclo[2.2.1]hept-5-ene-2-carboxylic acid, (1R,2R,4S)-2ethylbicyclo[2.2.1]hept-2-yl ester, rel-, polymer with

rel-(3aR, 4S, 5R, 7S, 7aR)-5-ethyloctahydro-4,7-methano-1H-inden-5-yl 2-methyl-2-propenoate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

290808-30-9 CRN CMF C17 H24 O2

Relative stereochemistry.

CM

CRN 271598-65-3 CMF C16 H24 O2

Relative stereochemistry.

CRN 108-31-6 CMF C4 H2 O3

REFERENCE COUNT:

THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L34 ANSWER 85 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 55

ACCESSION NUMBER:

2000:157963 HCAPLUS

DOCUMENT NUMBER:

132:201051

6

TITLE:

New photoresist-monomer with hydroxy groups and carboxyl groups, copolymer and photoresist

composition using the same

INVENTOR(S):

Lee, Geun Su; Koh, Cha Won; Jung, Jae Chang; Jung, Min

Ho; Baik, Ki Ho

PATENT ASSIGNEE(S):

Hyundai Electronics Industries Co., Ltd., Ichon, S.

Korea

SOURCE:

Ger. Offen., 28 pp.

CODEN: GWXXBX

DOCUMENT TYPE:

Patent German

LANGUAGE: FAMILY ACC. NUM. COUNT:

1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
DE 19940516	A1	20000309	DE 1999-19940516	19990826
KR 2000015013	A	20000315	KR 1998-34694	19980826
KR 2000020467	Α	20000415	KR 1998-39079	19980921
JP 2000086726	A2	20000328	JP 1999-238931	19990825
JP 3587743	B2	20041110		
NL 1012916	A1	20000229	NL 1999-1012916	19990826
NL 1012916	C2	20021203		
GB 2340831	A1	20000301	GB 1999-20124	19990826
GB 2340831	В2	20040512		
FR 2782715	A1	20000303	FR 1999-10819	19990826
FR 2782715	B1	20040910		
CN 1247858	Α	20000322	CN 1999-118357	19990826
IT 1307051	B1	20011023	IT 1999-TO725	19990826
US 6410670	B1	20020625	US 1999-383861	19990826
TW 535033	В	20030601	TW 1999-88114597	19990826
US 2002091216	A1	20020711	US 2002-79753	20020219
US 6586619	B2	20030701		
PRIORITY APPLN. INFO.:			KR 1998-34694	A 19980826
			KR 1998-39079	A 19980921
			US 1999-383861	A3 19990826

OTHER SOURCE(S):

MARPAT 132:201051

IT 260065-43-8P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(preparation of **photoresist** copolymer using new

photoresist-monomer for photoresist composition with

submicron resolution)

RN 260065-43-8 HCAPLUS

7-Oxabicyclo[2.2.1]hept-5-ene-2,3-dicarboxylic acid, mono(5-hydroxypentyl) ester, polymer with bicyclo[2.2.1]hept-2-ene, 1,1-dimethylethyl hydrogen bicyclo[2.2.1]hept-5-ene-2,3-dicarboxylate and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CN

CRN 260065-28-9 CMF C13 H18 O6

CM 2

CRN 76198-01-1 CMF C13 H18 O4

CM 3

CRN 498-66-8 CMF C7 H10



CM 4

CRN 108-31-6 CMF C4 H2 O3

L34 ANSWER 86 OF 86 HCAPLUS COPYRIGHT 2005 ACS on STN DUPLICATE 56

ACCESSION NUMBER: 1999:549311 HCAPLUS

DOCUMENT NUMBER:

INVENTOR(S):

131:170800

TITLE:

Modified polymers having polycyclic side chains Jayaraman, Saikumar; Benedikt, George M.; Rhodes,

Larry F.; Vicari, Richard; Allen, Robert D.; Dipietro,

Richard A.; Sooriyakumaran, Ratnam; Wallow, Thomas

PATENT ASSIGNEE(S): The B.F. Goodrich Company, USA

SOURCE:

PCT Int. Appl., 84 pp.

CODEN: PIXXD2

DOCUMENT TYPE:

Patent

LANGUAGE:

English

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PA	rent :	NO.			KIND DATE			APPLICATION NO.								DATE					
WO	9942	510			A1	19990826			WO 1999-US3771							19990219					
	W:	AL,	AM,	AU,	AZ,	BA,	BB,	BG,	BR,	BY	, c	Ά,	CN,	CZ,	EE,	GE,	HU,	ID,			
		IL,	IS,	JP,	KE,	KG,	KR,	KZ,	LC,	LK	, L	R,	LS,	LT,	LV,	MD,	MG,	MK,			
		MN,	MW,	MX,	NO,	NZ,	PL,	RO,	RU,	SD	, S	G,	SI,	SK,	SL,	ТJ,	TM,	TR,			
		TT,	UA,	UG,	UZ,	VN,	YU,	ZW,	AM,	ΑZ	, B	ΒY,	KG,	ΚZ,	MD,	RU,	ТJ,	TM			
	RW:	GH,	GM,	KE,	LS,	MW,	SD,	SZ,	UG,	ZW	, A	Τ,	BE,	CH,	CY,	DE,	DK,	ES,			
		FI,	FR,	GB,	GR,	ΙE,	IT,	LU,	MC,	NL	, P	T,	SE,	BF,	ВJ,	CF,	CG,	CI,			
		CM,					MR,														
AU									AU 1999-28724							.9990	219				
EP	P 1060206				A 1		2000	1220	EP 1999-909541							19990219					
EP	1060	206			В1		2004	0414													
	R:	AT,	BE,	CH,	DE,	DK,	ES,	FR,	GB,	GR	, I	Τ,	LI,	LU,	NL,	SE,	MC,	PT,			
		ΙE,	FI																		
JP	2002	5045	77		Т2		2002	0212		JP	200	0-5	5324	61		1	.9990	219			
US	6451	945			В1		2002	0917		US	199	9-2	2534	99		1	.9990	219			
AT	2643	52			E		2004	0415		AΤ	199	9-9	9095	41		1	.9990	219			
TW	5655	75			В		2003	1211						2555			.9990	407			
US	2003	0181	53		A1		2003	0123		US	200	2-2	2249	94		2	20020	821			
US	6794	459			В2		2004	0921													
PRIORIT	Y APP	LN.	INFO	.:						US	199	8-7	7555	8 P		P 3	.9980	223			
									US	199	9-2	2534	99		A3 1	.9990	219				
										WO	199	9-1	JS37'	71	1	W 1	.9990	219			

ΙT 239137-09-8DP, hydrolyzed

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(modified polymers having polycyclic side chains for

photoresists with improved hydrophilicity)

RN 239137-09-8 HCAPLUS

CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, 1,2,3,4,4a,5,8,8aoctahydro-, ethyl ester, polymer with 1,1-dimethylethyl

bicyclo[2.2.1]hept-5-ene-2-carboxylate, ethyl (3-methylbicyclo[2.2.1]hept-5-en-2-yl)methyl carbonate and trimethylsilyl bicyclo[2.2.1]hept-5-ene-2carboxylate (9CI) (CA INDEX NAME)

CM 1

CRN 239137-00-9 CMF C12 H18 O3

CRN 154970-45-3 CMF C12 H18 O2

3 CM

CRN 61615-20-1 CMF C15 H20 O2

CM

CRN 56151-01-0 CMF C11 H18 O2 Si

REFERENCE COUNT:

3 THERE ARE 3 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

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L15

(FILE 'HOME' ENTERED AT 12:14:41 ON 07 MAR 2005)

FILE 'REGISTRY' ENTERED AT 12:15:00 ON 07 MAR 2005 L1SCREEN 2067 L2 STRUCTURE UPLOADED QUE L2 AND L1 L3 0 S L3 SSS SAM L4

SCREEN 2067 L5 L6 STRUCTURE UPLOADED L7 QUE L6 AND L5

L8 0 S L7 SSS SAM L9 SCREEN 2067 STRUCTURE UPLOADED L10 L11 QUE L10 AND L9 50 S L11 SSS SAM L12

L13 SCREEN 2067 STRUCTURE UPLOADED L14 QUE L14 AND L13

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L16
             50 S L15 SSS SAM
L17
                SCREEN 2067
L18
                STRUCTURE UPLOADED
                QUE L18 AND L17
L19
L20
               SCREEN 2067
L21
               STRUCTURE UPLOADED
L22
                OUE L21 AND L20
L23
                SCREEN 2067
L24
               STRUCTURE UPLOADED
L25
                OUE L24 AND L23
L26
              4 S L25 SSS SAM
                SCREEN 2067
L27
                STRUCTURE UPLOADED
L28
                QUE L28 AND L27
L29
L30
              0 S L29 SSS SAM
     FILE 'HCAPLUS, CAPLUS, USPATFULL' ENTERED AT 12:22:28 ON 07 MAR 2005
           233 S L4 OR L8 OR L12 OR L16 OR L26 OR L30
L31
         454502 S PHOTORESIST OR RESIST
L32
           148 S L31 AND L32
L33
            86 DUPLICATE REMOVE L33 (62 DUPLICATES REMOVED)
L34
=> s 14
             0 L4
L35
=> s 18
L36
             0 L8
=> s 112
           210 L12
L37
=> d
L37 ANSWER 1 OF 210 HCAPLUS COPYRIGHT 2005 ACS on STN
    2005:123212 HCAPLUS
AN
DN
     142:198529
    Low polydispersity resin and preparation thereof using chain-transfer
TI
     Lee, Ting-Yu; Yu, Choa-Ying; Hsu, Meei-Yu; Wang, Shian-Jy; Ting, Ching;
IN
     Shih, Kuo-Chen
PA
     Taiwan
SO
    U.S. Pat. Appl. Publ., 13 pp.
     CODEN: USXXCO
DT
    Patent
    English
LA
FAN.CNT 1
                                            APPLICATION NO.
                                                                   DATE
     PATENT NO.
                         KIND
                                DATE
    US 2005032997
PΙ
                         A1
                                20050210
                                            US 2003-714052
                                                                   20031114
PRAI TW 2003-92121346
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COST IN U.S. DOLLARS
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FULL ESTIMATED COST
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STN INTERNATIONAL LOGOFF AT 12:25:27 ON 07 MAR 2005